

Features

This LSI has following features.

■ CPU

- Arm® Cortex®-A55, single-core
Max. operating frequency: 1.0GHz

■ Boot

- Support booting from Serial NAND / Serial NOR Flash

■ Internal memories and external memory interfaces

- On-chip shared SRAM (128 Kbytes with ECC)
- Built-in DDR3L-SDRAM (128-Mbytes)
1-channel memory controller for DDR3L-1600 with a 16-bit bus width
- SPI Multi I/O Bus Controller× 1 channel (4-bit Double data rate)
- SD card host interface × 1 channel

■ Video and Graphics

- 2D drawing engine

■ Display interfaces

- Selectable MIPI DSI × 1 channel or Digital parallel output × 1 channel

■ Various communication/storage/network interfaces

- USB2.0 × 1 channel (Host-Function)
- I2C Bus Interface × 2 channels
- Serial Communication Interface (SCI) × 2 channels
- Serial Communication Interface with FIFO (SCIF) × 5 channels
- Serial Peripheral Interface (RSPI) × 2 channels

■ Extended-function timers

- Multi-Function Timer Pulse Unit
32-bit × 1 channel, 16-bit × 8 channels

■ Audio

- Serial sound interface × 1 channels

■ Sensor

- Thermal Sensor Unit × 1 channel

Section 1 Overview

1.1 Outline of Specification

1.1.1 CPU Core

Item	Description
System CPU Cortex-A55	• Arm Cortex-A55 Single MPCore 1.0 GHz • L1 I-cache 32 Kbytes (Parity) / D-cache 32 Kbytes (ECC) • L2 cache 0 Kbyte • L3 cache 256 Kbytes (ECC) • Arm® NEON™ / FPU supported • Arm® v8.2-A architecture
Boot	• 5 boot modes - Boot Mode 3: Booting from a serial NOR flash memory (Single / Quad) connected to the SPI Multi I/O bus space (1.8 V) - Boot Mode 4: Booting from a serial NOR flash memory (Single / Quad) connected to the SPI Multi I/O bus space (3.3 V) - Boot Mode 5: Booting from SCIF download - Boot Mode 6: Booting from a serial NAND flash memory (Single / Quad) Connected to the SPI Multi I/O bus space (1.8V) - Boot Mode 7: Booting from a serial NAND flash memory (Single / Quad) Connected to the SPI Multi I/O bus space (3.3V)
Debug Interface	• Arm® CoreSight™ architecture • JTAG / SWD interface supported • ETF 16 Kbytes for program flow trace (each cluster)

1.1.2 CPU Peripheral

Item	Description
Clock Pulse Generator (CPG)	- Generates the clocks from external clock (EXCLK 24 MHz). Maximum Arm Cortex-A55 clock: 1.0 GHz Maximum DDR clock: 800 MHz (DDR3L-1600) Maximum DRW clock: 200 MHz Maximum AXI-bus clock: 200 MHz Maximum APB-bus clock: 100 MHz - SSC (Spread Spectrum Clock) supported
Direct Memory Access Controller (DMAC)	2 modules, 16 channels per module - Transfer request: On-chip peripheral request / auto request (software trigger) - A specific DMA transfer interval can be specified to adjust the bus occupancy. - LINK mode (DMA transfer under descriptor control) supported - Transfer information can be automatically reloaded
Interrupt Controller	- Arm® CoreLink™ Generic Interrupt Controller (GIC-600) for Arm Cortex-A55 - External Interrupt pins (NMI, IRQ7 to IRQ0, TINT31-0) - On-chip peripheral Interrupts: Priority level set for each module
General-purpose I/O (GPIO)	General-purpose I/O ports
Thermal Sensor Unit (TSU)	1 channel

1.1.3 Internal Memory

Item	Description
On-chip RAM	RAM of 128 Kbytes (ECC)

1.1.4 External Memory Interface

Item	Description
External Bus Controller for DDR3L SDRAM (DDR) *1	• Support DDR3L-1600 • Bus Width: 16-bit • Memory Size: 128M Bytes • Auto Refresh supported
SPI Multi I/O Bus Controller	• 1 channel (4-bit Double data rate) • 1 serial flash memory with multiple I/O bus sizes (single / quad) can be connected • External address space read mode (built-in read cache) • SPI operation mode • Maximum Clock Frequency: – 50 MHz (Quad-SPI DDR) – 66 MHz (Quad-SPI SDR)
SD Card Host Interface(SD)	• 1 channel • Channel 0 supports SDHI • SD memory I/O card interface (1-bit / 4-bit SD bus) • SD, SDHC and SDXC SD memory card access supported • Compliant with SD 3.0 • Default, high-speed, UHS-I/SDR50, SDR104 transfer modes supported • Error check function: CRC7 (Command), CRC16 (Data) • Card detection function, write protect supported

Note 1. This LSI is a SiP (system in package) with build-in DDR3L SDRAM, so customers cannot use DDR interface.

1.1.5 Video Processing Unit

Item	Description
2D drawing engine (DRW)	• Support almost any object geometry, rather than being bound to only a few specific geometries such as lines, triangles, or circles. The edges of every object can be independently blurred or anti-aliased • Color Formats - Frame buffer formats 8-bit: a (8) 16-bit: RGB (565), aRGB (4444), aRGB (1555) 32-bit: aRGB (8888) - Texture formats 1-bit: CLUT (1) / I (1) 2-bit: CLUT (2) / I (2) 4-bit: CLUT (4) / I (4) 16-bit: aRGB (4444), aRGB (1555), RGB (565) 24-bit: RGB (888) (run length encoded (RLE) unit) 32-bit: aRGB (8888). - CLUT formats use a 256-entry color lookup table.

1.1.6 Display Interface

Item	Description
LCD Controller	• 1 channel (Parallel output) • 2 planes blending (can blend 2 different size images) • Support Image Processing: – Dither processing (RGB666) – Clipping – RGB Gamma Correction LUT • Support Input Data Format: – RGB565 / RGB666 / RGB888 – ARGB1555 / ARGB4444 / ARGB8888 – YcbCr444 8-bit / YcbCr422 8-bit / YcbCr420 8-bit
MIPI DSI Interface	• 1 channel • The number of Lane: 4-lane • Support up to WXGA (1280 × 800), 60 fps (RGB888) • Maximum Bandwidth: 1.5 Gbps per lane • Support Output Data Format: – RGB666 / RGB888
Parallel Output Interface	• 1 channel • Support WXGA (1280 × 800), 60 fps • Support Output Data Format: – RGB666 / RGB888 • CLK / HD / VD timing signal supported

1.1.7 Sound Interface

Item	Description
Serial Sound Interface (SSI)	• 1 channel bidirectional serial transfer • 2 external clock sources available • Duplex communication • Support of I2S / Monaural / TDM audio formats • Support of master and slave functions • Generation of programmable word clock and bit clock • Multi-channel formats • Support of 8, 16, 18, 20, 22, 24, and 32-bit data formats • Support of 32-stage FIFO for transmission and reception • Support of LR-clock continue function in which the LR-clock signal is not stopped

1.1.8 Storage and Network

Item	Description
USB2.0 Host / Function (USB)	• 1 channel (Host-Function) • Compliance with USB2.0 • Supports Battery Charging Function • Internal dedicated DMA

1.1.9 Timer

Item	Description
Multi-function Timer Pulse Unit 3 (MTU3a)	• 9 channels (16 bits × 8 channels, 32 bits × 1 channel) • Module clock frequency (P0φ): 100 MHz • Maximum 28 lines of pulse inputs/outputs and 3 lines of pulse inputs • 14 types of count clocks selectable • Input capture function • 39 outputs compare and input capture registers • Counter clear operation (Simultaneous counter clearing by Compare match or Input capture is available) • Simultaneous writing to multiple timer counters (TCNT) • Synchronous input/output of each register due to synchronous operation of the counter • Buffered operation • Cascade-connected operation • 43 types of interrupt sources • Automatic transfer of register data • Pulse output modes - Toggle, PWM, complementary PWM, and reset-synchronized PWM modes • Synchronization of multiple counters • Phase counting mode – 16-bit mode (channel 1 and 2) – 32-bit mode (channel 1 and 2) • Counter function of dead time compensation • Digital filter functions for the input capture and external count clock pin
Port Output Enable 3 (POE3)	• Control of the high-impedance state of the MTU3a waveform output pins • Activation with four input pins • Activation on detection of short-circuited outputs • Activation by register write • Additional programming of output control target pins is possible.
Watchdog Timer (WDT)	• 1 channel • A counter overflow can reset the LSI • CPU parity error can reset the LSI
General Timer (GTM)	• 32 bits × 3 channels • Two operating modes – Interval timer mode – Free-running comparison mode

1.1.10 Peripheral Module

Item	Description
I2C Bus Interface (I2C)	• 2 channels (ch0 = Dedicated pin, ch1 = Multiplexed pin) • Master mode and slave mode supported • Support for 7-bit and 10-bit slave address formats • Support for multi-master operation • Timeout detection
Serial Communication Interface with FIFO (SCIFA)	• 5 channels • Clock synchronous mode or asynchronous mode selectable • Simultaneous transmission and reception (full-duplex communication) supported • Dedicated baud rate generator • Separate 16-byte FIFO registers for transmission and reception • Modem control function (channel 0, 1, and 2 in asynchronous mode)
Serial Communication Interface (SCIg)	• 2 channels • Clock synchronous mode, asynchronous mode, or smart card interface mode is selectable • Simultaneous transmission and reception (full-duplex communication) supported • Dedicated baud rate generator • LSB first / MSB first selectable • Modem control function • Encoding and decoding of IrDA communications waveforms in accord with version 1.0 of the IrDA standard (on channel 0)
Renesas Serial Peripheral Interface (RSPI)	• 2 channels • SPI operation • Master mode and slave mode supported • Programmable bit length, clock polarity, clock phase can be selected • Consecutive transfers • LSB first / MSB first selectable

1.1.11 Others

Item	Description
Boundary Scan	• Boundary scan based on IEEE 1149.1 via JTAG interface is supported. Note that some module pins are not available on this boundary scan.

1.1.12 Power Supply Voltage

Item	Description
Power supply voltage	• VDD, PLLn_DVDD11 (n = 23, 5): 1.05 to 1.15 V • DDR_VDDQn (n = 1,2): 1.283 to 1.45 V (DDR3L) • VDD18, JTAG_PVDD, PLLn_AVDD18 (n = 1, 23, 4, 5): 1.62 to 1.98 V • OTP_VDD18, USB_VDD18, DSI_VDD18: 1.65 to 1.95 V • PVDD: 2.97 to 3.63 V • USB_VDD33: 3.00 to 3.60 V • SDn_PVDD (n = 0), SPI_PVDD: 2.97 to 3.63 V / 1.70 to 1.95 V

1.1.13 Temperature Range

Item	Description
Temperature range	• T_a: -40°C to +85°C*1 • T_j: -40°C to +110°C

Note 1. If wider temp is required than this range, use case has to be investigated.

1.1.14 Quality level

Item	Description
Quality level	• Industrial usage, etc.

1.1.15 Package

Item	Description
Package	• 244-pin LFBGA, 17-mm square, 0.8-mm pitch

1.2 Block Diagram

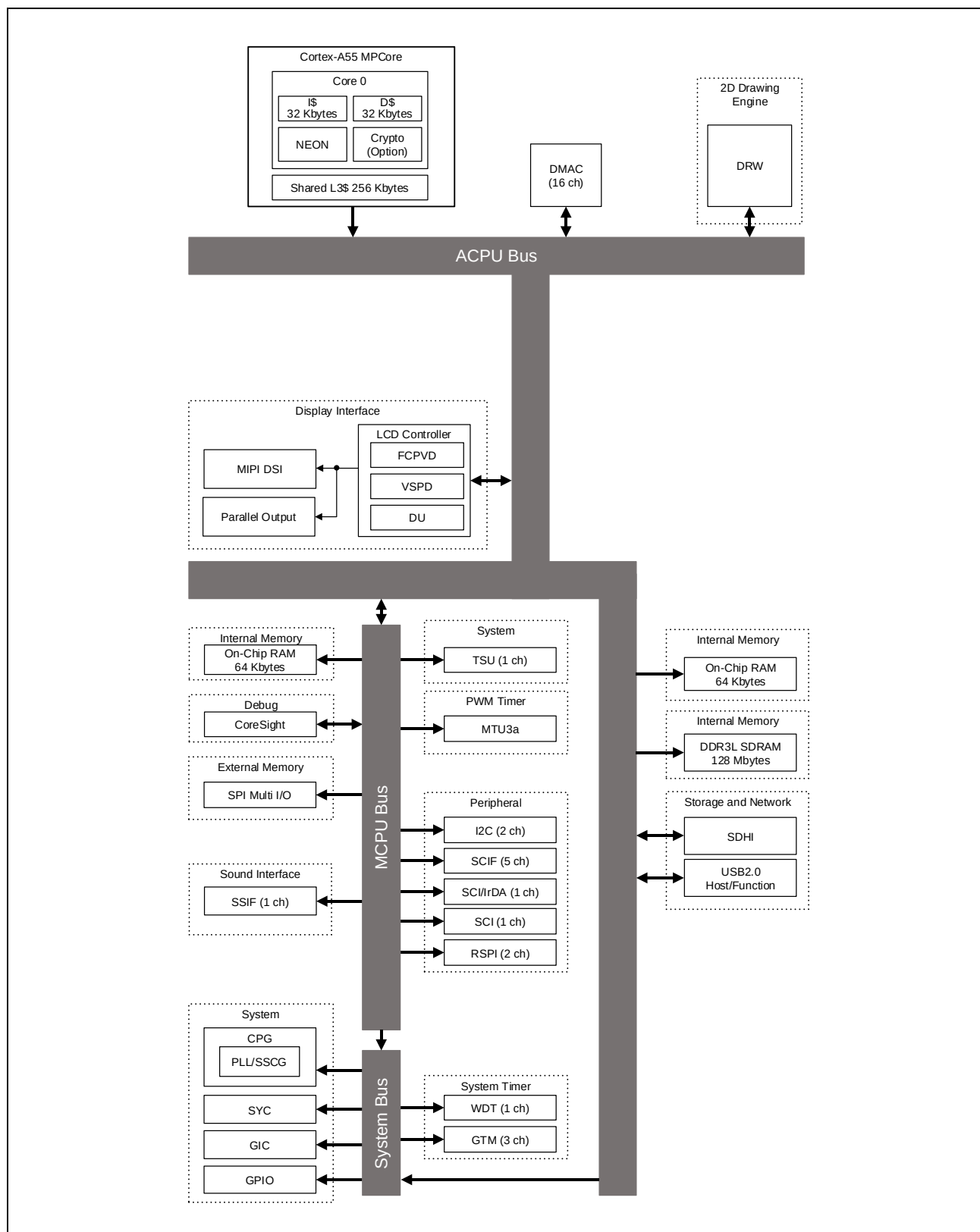


Figure 1.2–1 Block Diagram

1.3 Product Lineup

Table 1.3-1 Product Lineup

Group	RAM	Security	Part Number
RZ/A3M	128MByte	No-Security	R9A07G066M04GBG

Section 2 Pin

This section describes the pins of this LSI.

2.1 Pin Assignment

Refer to attached excel file for the “ball view” about pin assignment of this LSI.

(Please double-click the icon on the right side) 

2.2 External Pins and Multiplexed Functional Pins

Refer to attached excel file for the “pin function list” about information of external pins and multiplexed functional pins of this LSI (Please double-click the icon on the right side). 

Section 3 Electrical Characteristics

3.1 Absolute Maximum Ratings

Table 3.1 Absolute Maximum Ratings

Item		Symbol	Value	Unit
Power supply voltage (3.3 V)		PV _{DD}	−0.5 to +3.8	V
		USB_V _{DD33}		
Power supply voltage (1.8-V/3.3-V switchable)		SD0_PV _{DD}	−0.5 to +3.8	V
		SPI_PV _{DD}		
Power supply voltage (1.8 V)		V _{DD18}	−0.5 to +2.5	V
		PLL1_AV _{DD18}		
		PLL23_AV _{DD18}		
		PLL4_AV _{DD18}		
		PLL5_AV _{DD18}		
		DSI_V _{DD18}		
		USB_V _{DD18}		
		JTAG_PV _{DD}		
		OTP_V _{DD18}		
DDR power supply voltage (DDR3L)		DDR_VDDQ1, DDR_VDDQ2	−0.5 to +2.5	V
Power supply voltage (1.1-V)		V _{DD}	−0.5 to +1.5	V
		PLL23_DV _{DD11}		
		PLL5_DV _{DD11}		
Input voltage	3.3-V I/O input pins	—	−0.3 to 3.3-V power supply (PV _{DD} , USB_V _{DD33}) + 0.3	V
	1.8-V/3.3-V switchable I/O input pins	—	−0.3 to 1.8-V/3.3-V switchable power supply (SD0_PV _{DD} , SPI_PV _{DD}) + 0.3	V
	1.8-V I/O input pins	—	−0.3 to 1.8-V power supply (V _{DD18} , DSI_V _{DD18} , USB_V _{DD18}) + 0.3	V
Operating temperature	Ambient temperature	T _a	−40 to +85 *1	°C
	Junction temperature	T _j	−40 to +110	°C
Storage temperature	Ambient temperature	T _{stg}	−40 to +150	°C

Note 1. If wider temp is required than this range, use case has to be investigated.

3.2 Power Supply

Table 3.2 Power Supply

Item	Symbol	Min.	Typ.	Max.	Unit	Remarks
Power supply voltage (3.3 V)	PV _{DD}	2.97	3.30	3.63	V	—
Power supply voltage (1.8 V)	V _{DD18}	1.62	1.80	1.98	V	—
	JTAG_PVDD	1.62	1.80	1.98	V	—
	OTP_V _{DD18}	1.65	1.80	1.95	V	—
Power supply voltage (1.1 V)	V _{DD}	1.05	1.10	1.15	V	—
Power supply voltage (USB)	USB_V _{DD33}	3.00	3.30	3.60	V	—
	USB_V _{DD18}	1.65	1.80	1.95	V	—
Power supply voltage (SD)	SD0_PV _{DD}	2.97	3.30	3.63	V	When 3.3 V is supplied
		1.70	1.80	1.95	V	When 1.8 V is supplied
Power supply voltage (SPI)	SPI_PV _{DD}	2.97	3.30	3.63	V	When 3.3 V is supplied
		1.70	1.80	1.95	V	When 1.8 V is supplied
Power supply voltage (DSI)	DSI_V _{DD18}	1.65	1.80	1.95	V	—
Power supply voltage (DDR3L)	DDR_VDDQ1,	1.283	1.35	1.45	V	
	DDR_VDDQ2					
Power supply voltage (PLL)	PLL1_AV _{DD18} , PLL23_AV _{DD18} , PLL4_AV _{DD18} , PLL5_AV _{DD18}	1.62	1.80	1.98	V	—
	PLL23_DV _{DD11} , PLL5_DV _{DD11}	1.05	1.10	1.15	V	—

3.3 Power-On/Power-Off Sequence

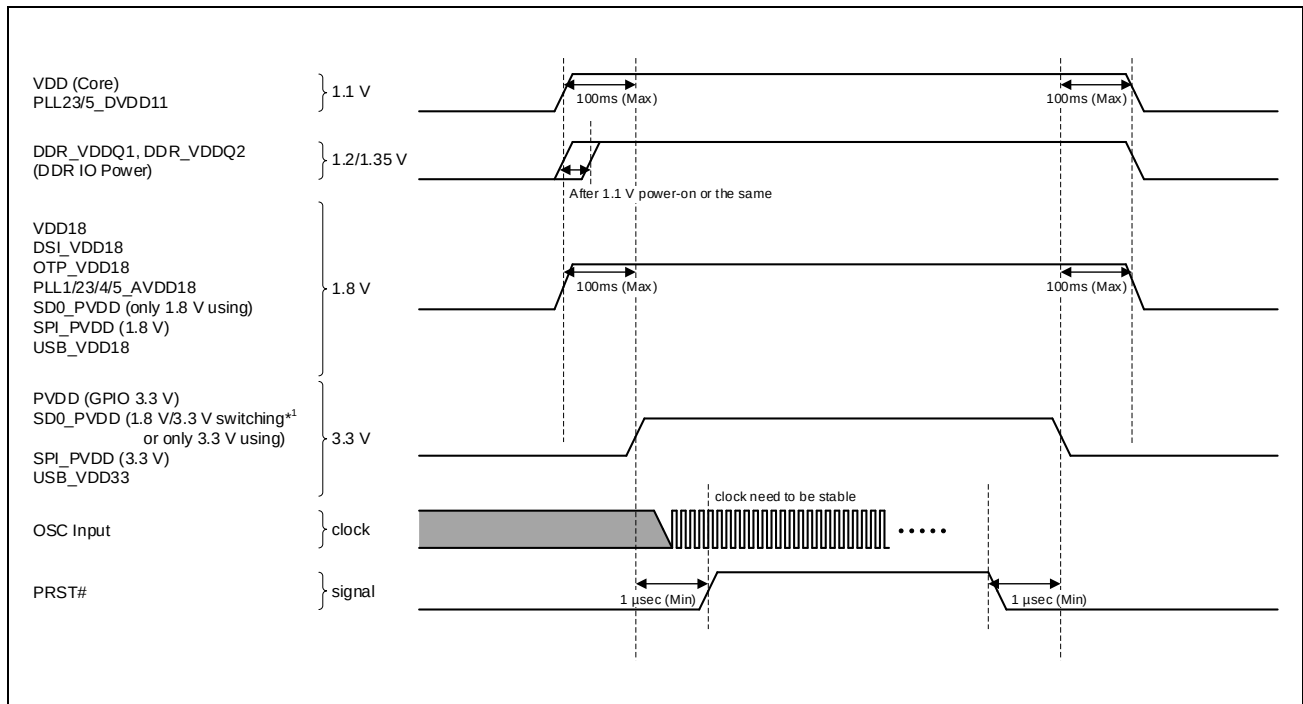


Figure 3.1 Power-On/Power-Off Sequence

NOTES

1. Turn on 3.3 V after 1.1 V/1.8 V.

Note 1. About SD0_PVDD, especially in the case of switching between 1.8 V and 3.3 V at same power rail, 1.8-V power-on/off timing can also follow 3.3-V power rail sequence as shown in the Figure 3.1.

2. Turn on the DDR IO power supply at the same time as or after the 1.1-V power supply.
3. From first power rising start to last power rising end must be within 100 ms.
4. The power-off sequence is the reverse of the power-on sequence (PRST# → Low ⇒ 3.3 V = OFF ⇒ Other = OFF)
5. PRST# should be changed from Low to High after the 3.3-V power supply is turned on, after 1 μsec, and after the input clock from the oscillator stabilizes.

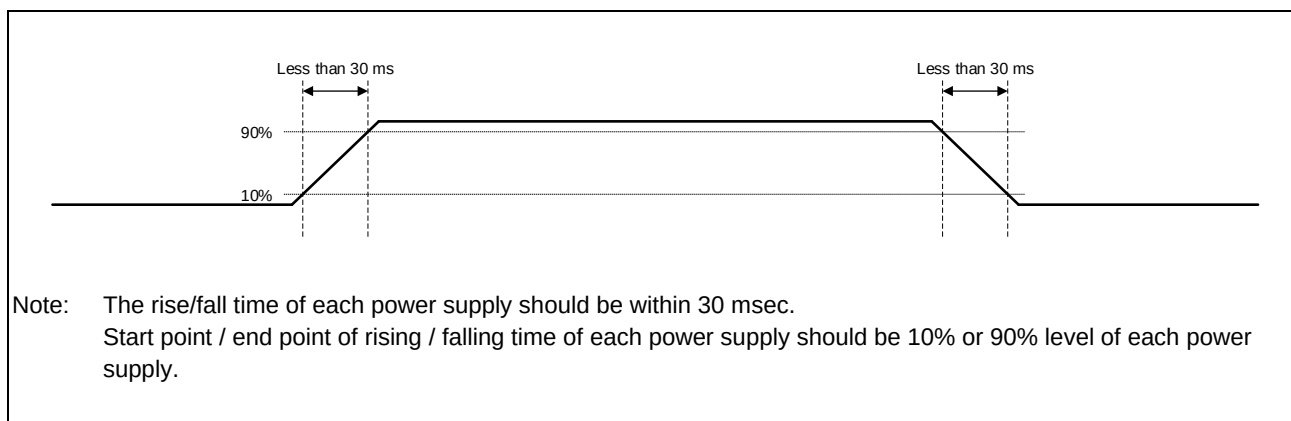


Figure 3.2 Power Up Time/Power Down Time (1)

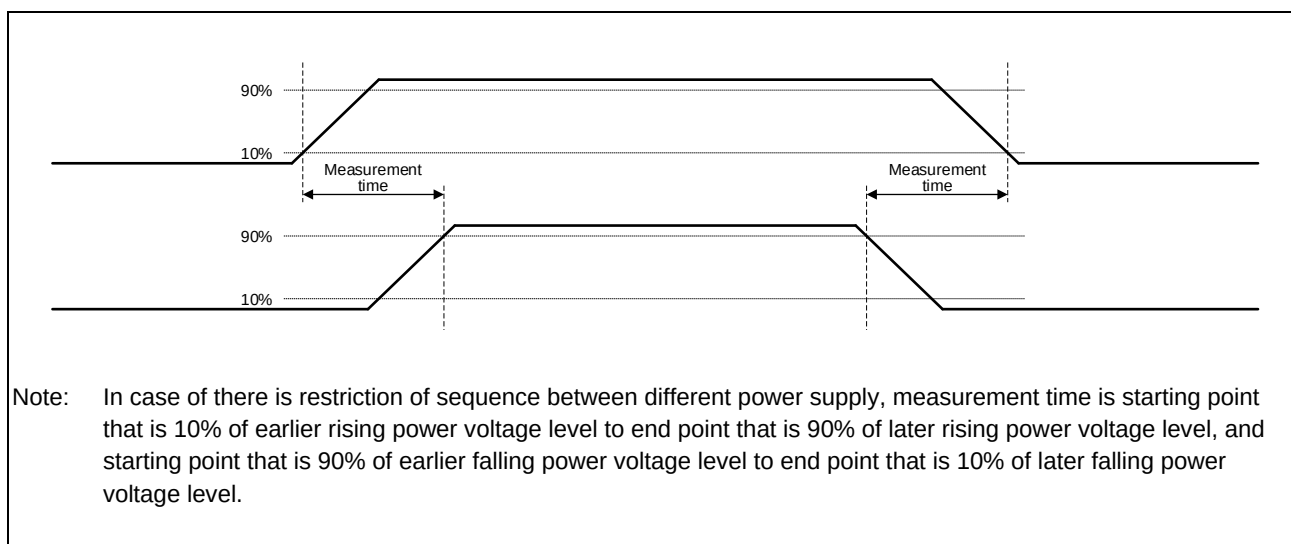


Figure 3.3 Power Up Time/Power Down Time (2)

3.4 DC Characteristics

Table 3.3 DC Characteristics (1) [3.3-V I/O]

Item	Symbol	Min.	Typ.	Max.	Unit	Remarks
High-level input voltage	V_{IH}	2	—	$PV_{DD} + 0.3$	V	
Low-level input voltage	V_{IL}	-0.3	—	0.8	V	
Hysteresis threshold $\uparrow$	V_{T+}	0.9	—	2.1	V	
Hysteresis threshold $\downarrow$	V_{T-}	0.7	—	1.9	V	
Input hysteresis voltage	V_{HYS}	0.306	—	0.420	V	
Output logic high voltage	V_{OH}	$PV_{DD} - 0.4$	—	PV_{DD}	V	
	($I_{OH} = -2mA$)					
	($I_{OH} = -4mA$)					
	($I_{OH} = -8mA$)					
	($I_{OH} = -12mA$)					
Output logic low voltage	V_{OL}	0	—	0.4	V	
	($I_{OL} = 2mA$)					
	($I_{OL} = 4mA$)					
	($I_{OL} = 8mA$)					
	($I_{OL} = 12mA$)					
Weak pull-up resistor (input mode)	R_{UP}	7K	—	100K	Ω	
Weak pull-down resistor (input mode)	R_{DN}	7K	—	100K	Ω	

Note 1. Schmitt can be used at only RIIC mode.

Table 3.4 DC Characteristics (2) [1.8-V I/O]

Item	Symbol	Min.	Typ.	Max.	Unit	Remarks
High-level input voltage	V_{IH}	$0.65 \times V_{DD18}$	—	$V_{DD18} + 0.3$	V	
Low-level input voltage	V_{IL}	-0.3	—	$0.35 \times V_{DD18}$	V	
Output logic high voltage	V_{OH}	$V_{DD18} - 0.4$	—	V_{DD18}	V	
	($I_{OH} = -2mA$)					
	($I_{OH} = -4mA$)					
	($I_{OH} = -8mA$)					
	($I_{OH} = -12mA$)					
Output logic low voltage	V_{OL}	0	—	0.4	V	
	($I_{OL} = 2mA$)					
	($I_{OL} = 4mA$)					
	($I_{OL} = 8mA$)					
	($I_{OL} = 12mA$)					

Table 3.5 DC Characteristics (3) [3.3-V Input]

Item	Symbol	Min.	Typ.	Max.	Unit	Remarks
High-level input voltage	V_{IH}	2.3	—	$PV_{DD} + 0.3$	V	
Low-level input voltage	V_{IL}	-0.3	—	0.8	V	
Hysteresis threshold $\uparrow$	V_{T+}	0.9	—	2.1	V	
Hysteresis threshold $\downarrow$	V_{T-}	0.7	—	1.9	V	
Input hysteresis voltage	V_{HYS}	0.306	—	0.420	V	

Table 3.6 DC Characteristics (4) [1.8-V Input]

Item	Symbol	Min.	Typ.	Max.	Unit	Remarks
High-level input voltage	V_{IH}	$0.65 \times V_{DD18}$	—	$V_{DD18} + 0.3$	V	
Low-level input voltage	V_{IL}	-0.3	—	$0.35 \times V_{DD18}$	V	

Table 3.7 DC Characteristics (5) [3.3 V I/O (SD, QSPI)]

Item	Symbol	Min.	Typ.	Max.	Unit	Remarks
High-level input voltage	V_{IH}	$0.625 \times$ SDn_PV_{DD}	—	$SDn_PV_{DD} + 0.3$	V	
Low-level input voltage	V_{IL}	$SDn_PV_{DD} - 0.3$	—	$0.25 \times$ SDn_PV_{DD}	V	
Output logic high voltage	V_{OH}	$0.75 \times$ SDn_PV_{DD}	—	SDn_PV_{DD}	V	
	($\times 0.5$)					
	($\times 0.75$)					
	($\times 1.0$)					
	($\times 1.5$)					
Output logic low voltage	V_{OL}	0	—	$0.125 \times$ SDn_PV_{DD}	V	
	($\times 0.5$)					
	($\times 0.75$)					
	($\times 1.0$)					
	($\times 1.5$)					

Note: n = 0

Table 3.8 DC Characteristics (6) [1.8 V I/O (SD, QSPI)]

Item	Symbol	Min.	Typ.	Max.	Unit	Remarks
High-level input voltage	V_{IH}	1.27	—	2.00	V	
Low-level input voltage	V_{IL}	$SDn_PV_{DD} - 0.3$	—	0.58	V	
Output logic high voltage	V_{OH}	$0.8 \times SDn_PV_{DD}$	—	SDn_PV_{DD}	V	
	($\times 0.5$)					
	($\times 0.75$)					
	($\times 1.0$)					
	($\times 1.5$)					
Output logic low voltage	V_{OL}	0	—	$0.2 \times SDn_PV_{DD}$	V	
	($\times 0.5$)					
	($\times 0.75$)					
	($\times 1.0$)					
	($\times 1.5$)					

Note: n = 0

Table 3.9 DC Characteristics(7) [I²C Open Drain 3.3 V I/O]

Item	Symbol	Min.	Typ.	Max.	Unit	Remarks
External pull-up supply	V_{VDDP}	2.7	—	PV_{DD}	V	
Input high voltage	V_{IH}	$0.7 \times V_{VDDP}$	—	$V_{VDDP} + 0.5$	V	
Input Low Voltage	V_{IL}	-0.5	—	$0.3 \times V_{VDDP}$	V	
Low level output current	I_{OL}	20	—	—	mA	$V_{OL} = 0.4$ V
Low level output voltage	V_{OL}	—	—	0.4	V	$V_{VDDP} > 2$ V
Input hysteresis	V_{HYST}	$0.1 \times V_{VDDP}$	—	—	mV	

Table 3.10 DC Characteristics (8) [1.35-V Input (DDR3L)]

Item	Symbol	Min.	Typ.	Max.	Unit	Remarks
DC input high level	$V_{IH}(DC)$	$V_{REF} + 0.09$	—	—	V	
DC input low level	$V_{IL}(DC)$	—	—	$V_{REF} - 0.09$		$V_{REF} = 0.5 \times DDR_V_{DDQ}$
AC input high level	$V_{IH}(AC)$	$V_{REF} + 0.135$	—	—	V	
AC input low level	$V_{IL}(AC)$	—	—	$V_{REF} - 0.135$	V	$V_{REF} = 0.5 \times DDR_V_{DDQ}$
DC differential input high	V_{IHdiff}	0.18	—	—	V	
DC differential input low	V_{ILdiff}	—	—	-0.18	V	
AC differential input high	$V_{IHdiff}(AC)$	$2 \times (V_{IH}(AC) - V_{REF})$	—	—	V	
AC differential input low	$V_{ILdiff}(AC)$	—	—	$2 \times (V_{REF} - V_{IL}(AC))$	V	$V_{REF} = 0.5 \times DDR_V_{DDQ}$
Differential input cross point voltage relative to $0.5 \times DDR_V_{DDQ}$ for DQS	$V_{IX}(DQS)$	-0.075	—	0.075	V	

Table 3.11 DC Characteristics (9) [1.35-V Output (DDR3L)]

Item	Symbol	Min.	Typ.	Max.	Unit	Remarks
DC output high measurement level (for IV curve linearity)	$V_{OH}(DC)$	—	$0.8 \times DDR_V_{DDQ}$	—	V	The swing of $\pm 0.1 \times DDR_V_{DDQ}$ is based on approximately 50% of the static single-ended output high or low swing with a driver impedance of 40Ω and an effective test load of 25Ω to $V_{TT} = DDR_V_{DDQ}/2$.
DC output mid measurement level (for IV curve linearity)	$V_{OM}(DC)$	—	$0.5 \times DDR_V_{DDQ}$	—	V	
DC output low measurement level (for IV curve linearity)	$V_{OL}(DC)$	—	$0.2 \times DDR_V_{DDQ}$	—	V	
AC output high measurement level (for output slew rate)	$V_{OH}(AC)$	—	$V_{TT} + 0.1 \times DDR_V_{DDQ}$	—	V	
AC output low measurement level (for output slew rate)	$V_{OL}(AC)$	—	$V_{TT} - 0.1 \times DDR_V_{DDQ}$	—	V	

Table 3.12 DC Characteristics (10) [DDR3L Cross Point Voltage For Differential Output Signals (CK/DQS)]

Item	Symbol	Min.	Typ.	Max.	Unit	Remarks
Differential output cross point voltage relative to $0.5 \times DDR_V_{DDQ}$	$V_{OX}(CK/DQS)$	-0.1	—	0.1	V	

Table 3.13 DC Characteristics (11) [USB 2.0]

Item	Symbol	Min.	Typ.	Max.	Unit	Remarks
Input levels for low/full speed						
High (driven)	V_{IH}	2.0	—	—	V	
Low	V_{IL}	—	—	0.8	V	
Differential input sensitivity	V_{DI}	0.2	—	—	V	
Differential common mode range	V_{CM}	0.8	—	2.5	V	
Input levels for high speed						
High-speed squelch detection threshold (differential signal amplitude)	V_{HSSQ}	100	—	150	mV	
High-speed data signaling common mode voltage range (guideline for receiver)	V_{HSCM}	-50	—	500	mV	
Output levels for low/full speed						
Low	V_{OL}	0.0	—	0.3	V	
High (driven)	V_{OH}	2.8	—	3.6	V	
Output signal crossover voltage	V_{CRS}	1.3	—	2.0	V	
Output levels for high-speed						
High-speed idle level	V_{HSOI}	-10.0	—	10.0	mV	
High-speed data signaling high	V_{HSOH}	360	—	440	mV	
High-speed data signaling low	V_{HSOL}	-10.0	—	10.0	mV	
Chirp J level (differential voltage)	V_{CHIRPJ}	700	—	1100	mV	
Chirp K level (differential voltage)	V_{CHIRPK}	-900	—	-500	mV	

Table 3.14 DC Characteristics (12) [Current Consumption]

Item	Symbol	Max Current	Unit	Remarks
Power Supply voltage(3.3V)	PVDD	690.00	mA	PVDD = 3.63V
Power Supply voltage(1.8V)	JTAG_PVDD	10.00	mA	JTAG_PVDD = 1.98V
	OTP_VDD18	20.00	mA	OTP_VDD18 = 1.95V
	VDD18	10.00	mA	VDD18 = 1.98V
Power Supply voltage(1.1V)	VDD	1870.00	mA	VDD = 1.15V
Power supply voltage (USB/3.3V)	USB_VDD33	20.00	mA	USB_VDD33 = 3.60V
Power supply voltage (USB/1.8V)	USB_VDD18	140.00	mA	USB_VDD18 = 1.95V
Power supply voltage (SD/3.3V)	SD0_PVDD	220.00	mA	SD0_PVDD = 3.63V
Power supply voltage (SD/1.8V)	SD0_PVDD	70.00	mA	SD0_PVDD = 1.95V
Power supply voltage (SPI/3.3V)	SPI_PVDD	50.00	mA	SPI_PVDD = 3.63V
Power supply voltage (SPI/1.8V)	SPI_PVDD	90.00	mA	SPI_PVDD = 1.95V
Power supply voltage (DSI/1.8V)	DSI_VDD18	100.00	mA	DSI_VDD18 = 1.95V
Power supply voltage (DDR/1.35V)	DDR_VDDQ1	410.00	mA	DDR_VDDQ1 = 1.45V
	DDR_VDDQ2			DDR_VDDQ2 = 1.45V
Power supply voltage (PLL/1.8V)	PLL1_AVDD18	10.00	mA	PLL1_AVDD18 = 1.98V
	PLL23_AVDD18	20.00	mA	PLL23_AVDD18 = 1.98V
	PLL4_AVDD18	10.00	mA	PLL4_AVDD18 = 1.98V
	PLL5_AVDD18	10.00	mA	PLL5_AVDD18 = 1.98V
Power supply voltage (PLL/1.1V)	PLL23_DVDD11	20.00	mA	PLL23_DVDD11 = 1.15V
	PLL5_DVDD11	10.00	mA	PLL5_DVDD11 = 1.15V

Note: Tj : Max Condition

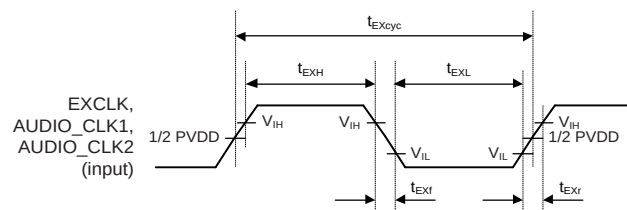
3.5 AC Characteristics

Conditions: $V_{DD} = PLL23_DV_{DD11} = PLL5_DV_{DD11} = 1.1 \pm 0.05 \text{ V}$,
 $PLL1_AV_{DD18} = PLL23_AV_{DD18} = PLL4_AV_{DD18} = 1.8 \pm 0.18 \text{ V}$,
 $V_{DD18} = JTAG_PV_{DD} = 1.8 \pm 0.18 \text{ V}$, $OTP_V_{DD18} = 1.8 \text{ V} \pm 0.15 \text{ V}$,
 $USB_V_{DD18} = DSI_V_{DD18} = 1.8 \pm 0.15 \text{ V}$,
 $PV_{DD} = 3.3 \pm 0.33 \text{ V}$, $USB_V_{DD33} = 3.3 \pm 0.3 \text{ V}$, $DDR_V_{DDQ} = 1.2 \pm 0.06 \text{ V}/1.283 \text{ to } 1.45 \text{ V}$,
 $SPI_PV_{DD} = SDn_PV_{DD} (n = 0) = 3.3 \pm 0.33 \text{ V}/1.70 \text{ to } 1.95 \text{ V}$, $V_{SS} = 0 \text{ V}$,
 $T_a = -40 \text{ to } +85^\circ\text{C}$, $T_j = -40 \text{ to } +110^\circ\text{C}$

3.5.1 Clock Timing

Table 3.15 Clock Timing Table

Item	Symbol	Min.	Max.	Unit	Figures
EXCLK clock input frequency	f_{EX}	24 – 100ppm	24 + 100ppm	MHz	Figure 3.4
EXCLK clock input cycle time	t_{EXcyc}	41.67	41.67	ns	
AUDIO_CLK1, AUDIO_CLK2 clock input frequency (external clock is input)	f_{EX}	10	50	MHz	
AUDIO_CLK1, AUDIO_CLK2 clock input cycle time (external clock is input)	t_{EXcyc}	20	100	ns	
EXCLK, AUDIO_CLK1, AUDIO_CLK2 clock input low level pulse width	t_{EXL}	0.4	0.6	t_{EXcyc}	
EXCLK, AUDIO_CLK1, AUDIO_CLK2 clock input high level pulse width	t_{EXH}	0.4	0.6	t_{EXcyc}	
EXCLK, AUDIO_CLK1, AUDIO_CLK2 clock input rise time	t_{EXr}	—	4	ns	
EXCLK, AUDIO_CLK1, AUDIO_CLK2 clock input fall time	t_{EXf}	—	4	ns	
Oscillator stabilization time	t_{OSC}	—	1	ms	Figure 3.5, Figure 3.6
Mode hold time	t_{MDH}	—	100	ns	
Mode setup time	t_{MDS}	—	100	ns	



Note: When the clock is input on the EXCLK, AUDIO_CLK1 or AUDIO_CLK2

Figure 3.4 EXCLK, AUDIO_CLK1 and AUDIO_CLK2 Clock Input Timing

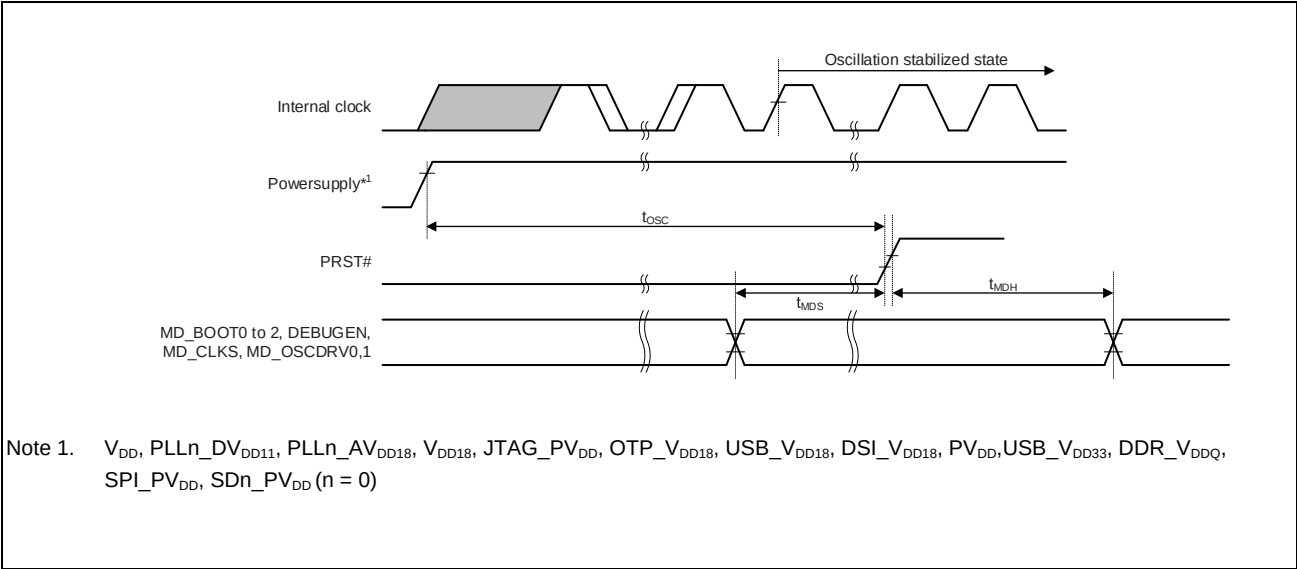


Figure 3.5 Power-On Oscillation Settling Time

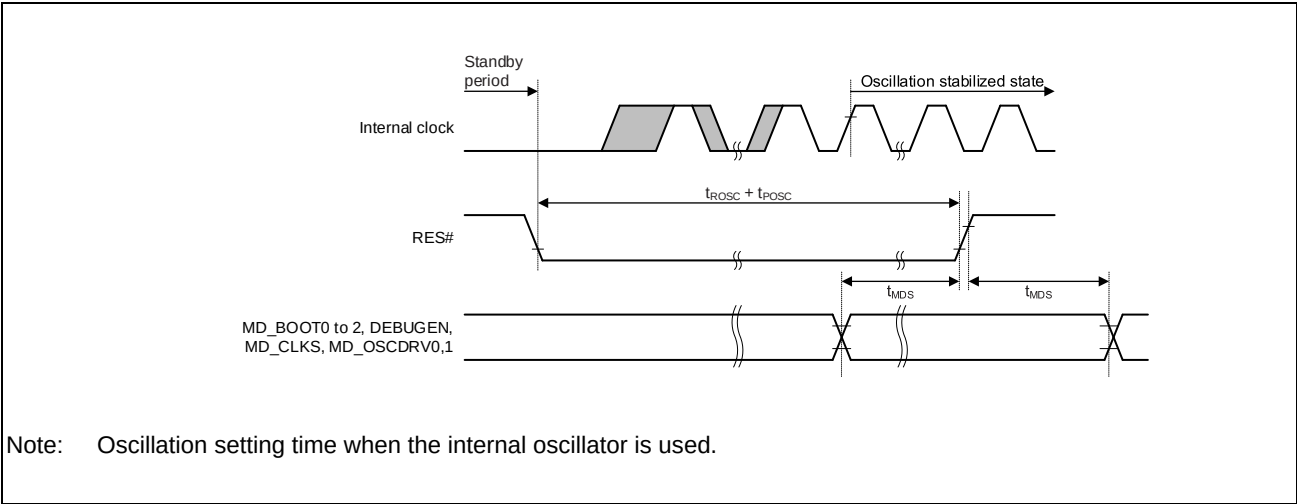


Figure 3.6 Oscillation Settling Time on Return from Standby (Return by Reset)

3.5.2 SDHI Access Timing

3.5.2.1 SDHI Access Timing (SDR 3.3-V)

Table 3.16 SDHC AC Access Timing (SDR at 3.3-V Operation)

Item	Symbol	Default Speed Mode (16.67 MHz)		High Speed Mode (33.33 MHz)		Unit	Figures
		Min.	Max.	Min.	Max.		
SD_CLK clock cycle	t_{SDCYC}	60.00	—	30.0	—	ns	Figure 3.7
SD_CLK clock high level width	t_{SDWH}	23.50	—	13.50	—	ns	
SD_CLK clock low level width	t_{SDWL}	23.50	—	13.50	—	ns	
SD_CLK clock rise time	t_{SDLH}	—	10	—	3	ns	
SD_CLK clock fall time	t_{SDHL}	—	10	—	3	ns	
SD_CMD,SD_DATA output delay	t_{SDODLY}	-4.50	4.0	-4.50	4.0	ns	
SD_CMD,SD_DATA input set up time	t_{SDIS}	5.5	—	5.5	—	ns	
SD_CMD,SD_DATA input hold time	t_{SDIH}	2.0	—	2.0	—	ns	
SD_CMD,SD_DATA input data width	t_{SDIDW}	—	—	—	—	ns	

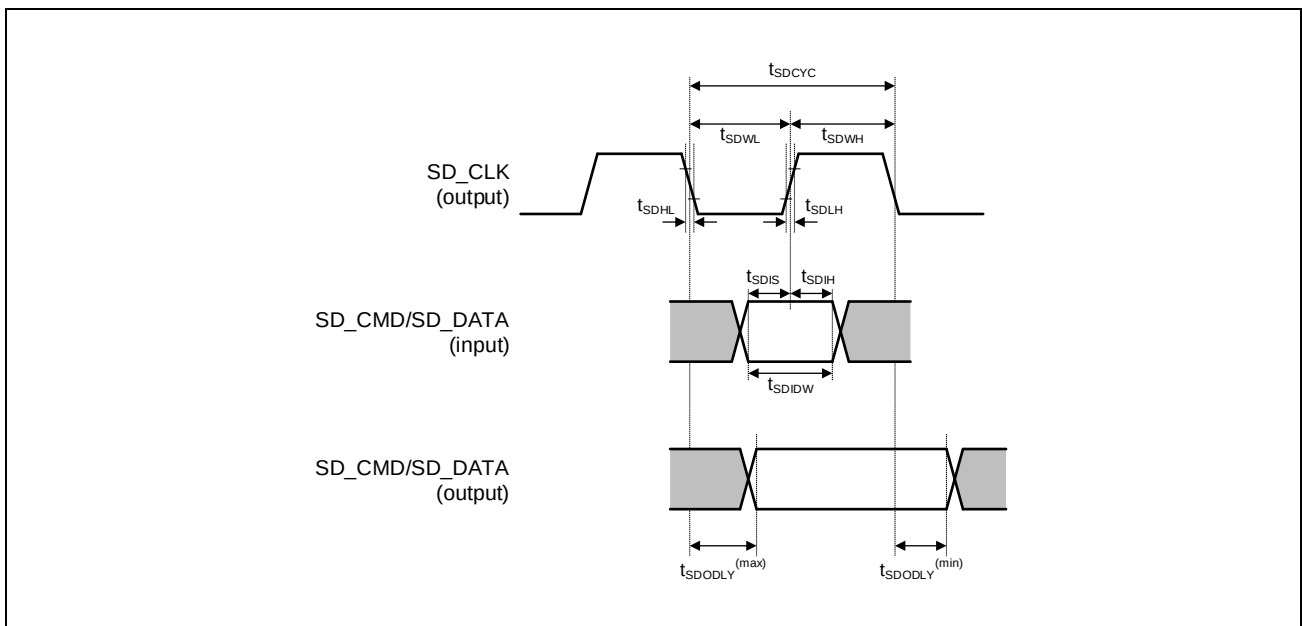


Figure 3.7 SDHC Interface Timing (SDR 3.3-V Power Supply)

NOTE

The disclosure of other characteristics of the SD interface needs the conclusion of the following agreement.

- SD Host/Ancillary Product License Agreement (SD HALA)

For details, contact your local sales representatives.

3.5.3 LCDC Access Timing

Table 3.17 LCDC AC Access Timing

Item	Symbol	Min.	Max.	Unit	Figures
DCLK period	t_{Lcyc}	11.5	172.33	ns	Figure 3.8
DCLK low pulse width	t_{LOL}	$t_{Lcyc}/2 - 1.06$	$t_{Lcyc}/2 + 1.06$	ns	
DCLK high pulse width	t_{LOH}	$t_{Lcyc}/2 - 1.06$	$t_{Lcyc}/2 + 1.06$	ns	
DCLK rise time	t_{LOR}	—	3	ns	
DCLK fall time	t_{LOF}	—	3	ns	
Data output dealy	t_{DD}	-1.5	1.5	ns	

Note: AC access timing condition: SR = 1 (fast) / Drive capacity setting 12 mA / Load capacity 30 pF.

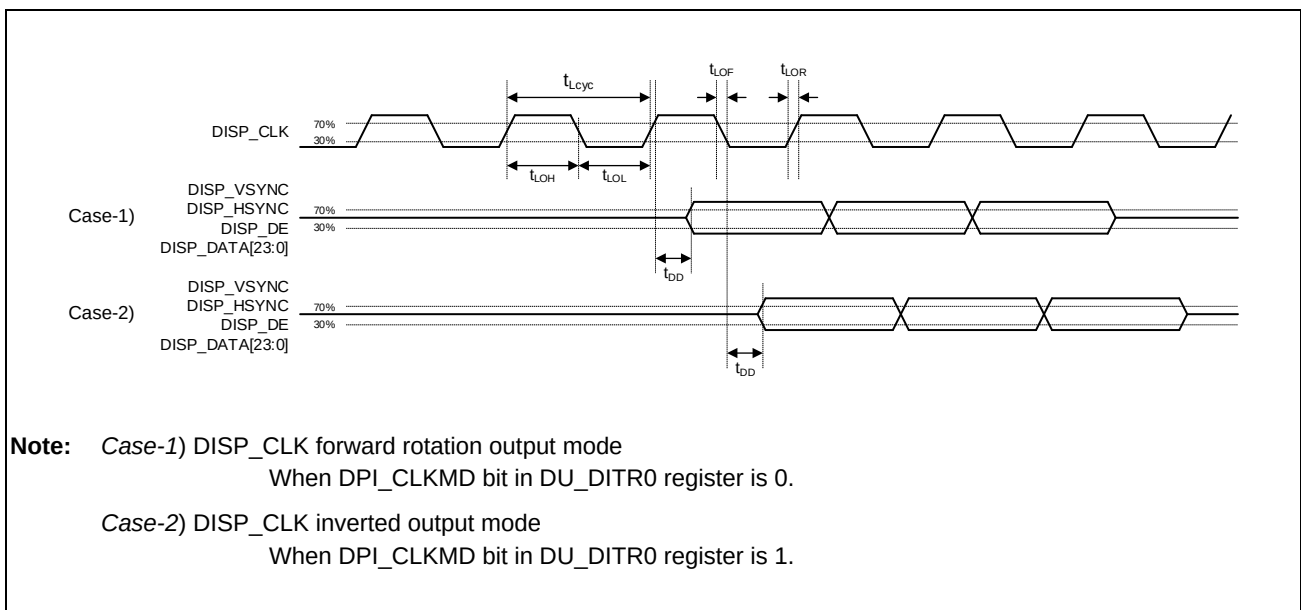


Figure 3.8 LCDC AC Access Timing

3.5.4 USB 2.0 Host/Function Module Access Timing

3.5.4.1 USB 2.0 Low-Speed Access Timing

Table 3.18 USB Transceiver Timing (Low-Speed)

Item	Symbol	Min.	Max.	Unit	Figures
Rise time	t_{LR}	75	300	ns	Figure 3.9
Fall time	t_{LF}	75	300	ns	
Rise/fall time lag	t_{LR}/t_{LF}	80	125	%	

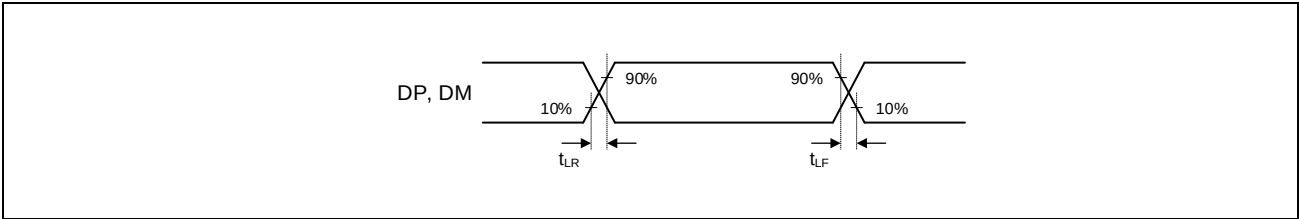


Figure 3.9 USB0_DP, USB1_DP, USB0_DM, and USB1_DM Output Timing (Low-Speed)

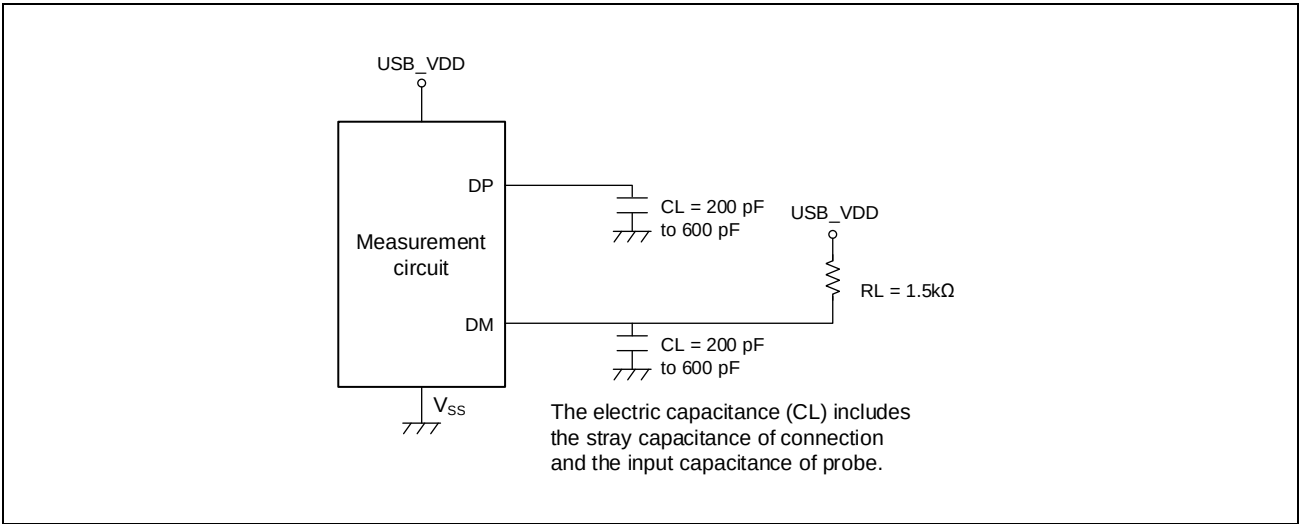


Figure 3.10 Measurement Circuit (Low-Speed)

3.5.4.2 USB 2.0Full-Speed Access Timing

Table 3.19 USB Transceiver Timing (Full-Speed)

Item	Symbol	Min.	Max.	Unit	Figures
Rise time	t_{FR}	4	20	ns	Figure 3.11
Fall time	t_{FF}	4	20	ns	
Rise/fall time lag	t_{FR}/t_{FF}	90	111.11	%	

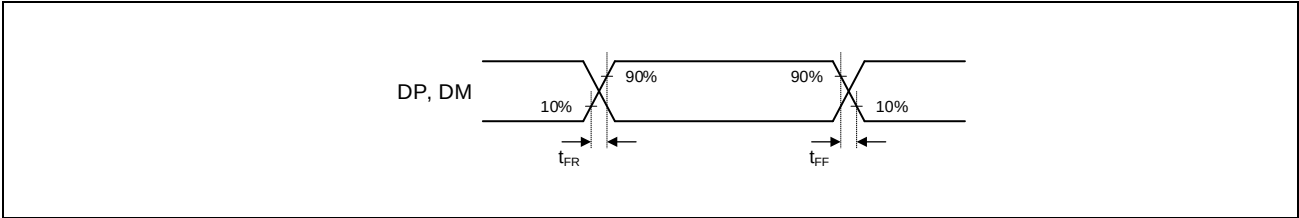


Figure 3.11 USB0_DP, USB1_DP, USB0_DM, and USB1_DM Output Timing (Full-Speed)

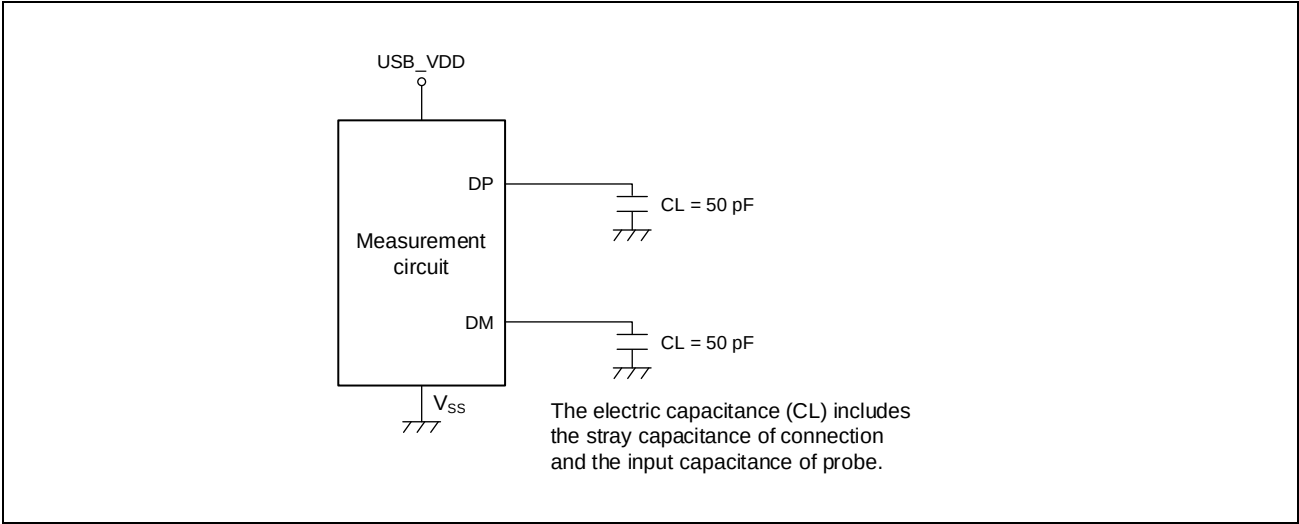


Figure 3.12 Measurement Circuit (Full-Speed)

3.5.4.3 USB 2.0 Hi-Speed Access Timing

Table 3.20 USB Transceiver Timing (Hi-Speed)

Item	Symbol	Min.	Max.	Unit	Figures
Rise edge rate	t_{HSR}	—	2133	V/ μ s	Figure 3.13
Fall edge rate	t_{HSF}	—	2133	V/ μ s	
Output driver resistance	Z_{HSDRV}	40.5	49.5	Ω	

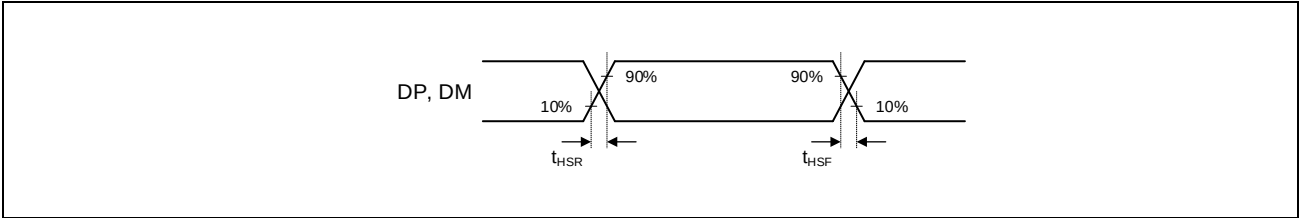


Figure 3.13 USB0_DP, USB1_DP, USB0_DM, and USB1_DM Output Timing (Hi-Speed)

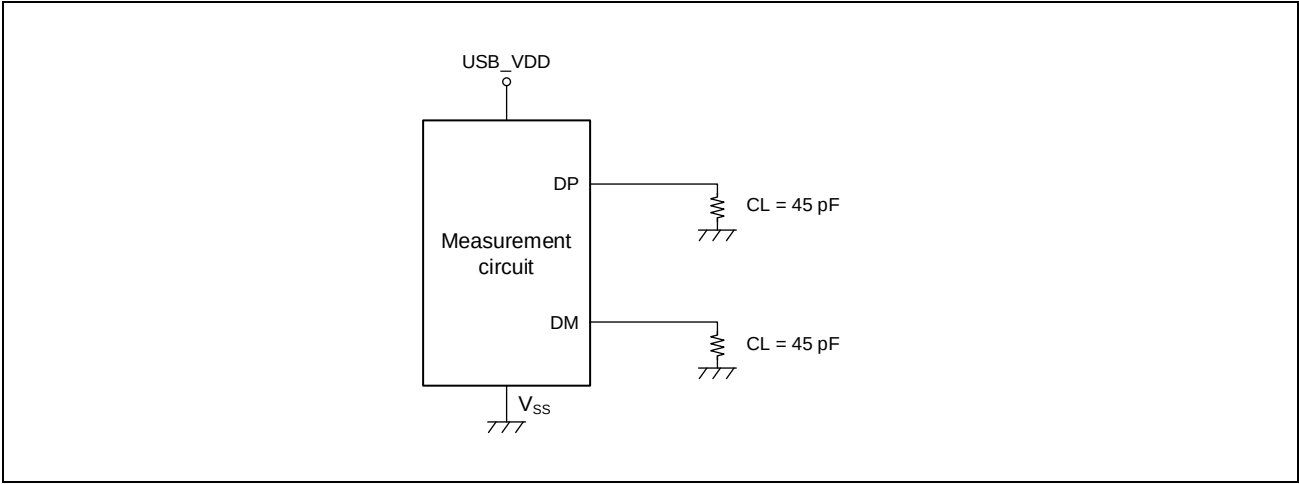


Figure 3.14 Measurement Circuit (Hi-Speed)

3.5.5 JTAG Debugger Interface Access Timing

Table 3.21 Debugger IF Timing

Item	Symbol	Min.	Max.	Unit	Figures
TCK_SWCLK cycle time	t_{TCKcyc}	50	—	ns	Figure 3.15
TCK_SWCLK high pulse width	t_{TCKH}	20	—	ns	Figure 3.16
TCK_SWCLK low pulse width	t_{TCKL}	20	—	ns	
TDI setup time	t_{TDIS}	15	—	ns	
TDI hold time	t_{TDIH}	15	—	ns	
TMS_SWDIO setup time	t_{TMSS}	15	—	ns	
TMS_SWDIO hold time	t_{TMSh}	15	—	ns	
SWDIO delay time	t_{SWDO}	—	14	ns	
TDO delay time	t_{TDOD}	—	14	ns	
Capture register setup time	t_{CAPTS}	10	—	ns	Figure 3.17
Capture register hold time	t_{CAPTH}	10	—	ns	
Update register delay time	$t_{UPDATED}$	—	20	ns	

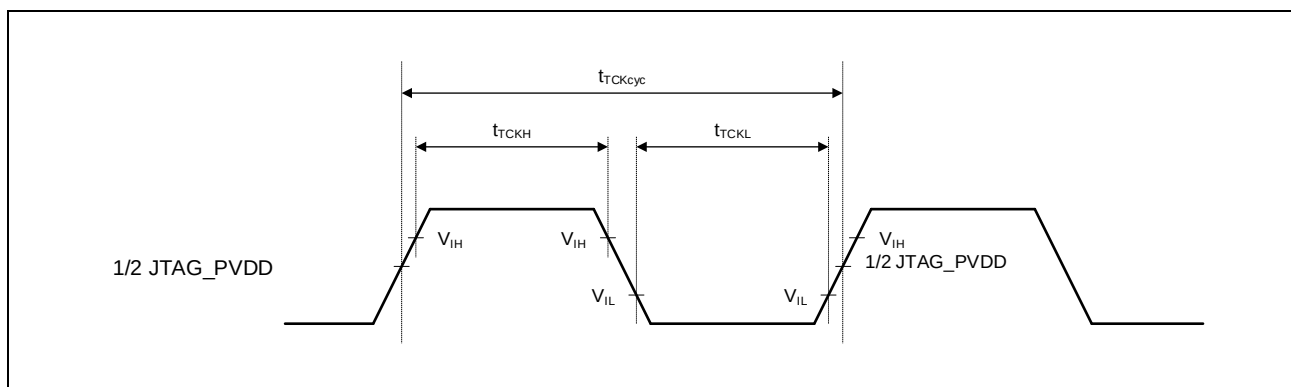


Figure 3.15 TCK_SWCLK Input Timing

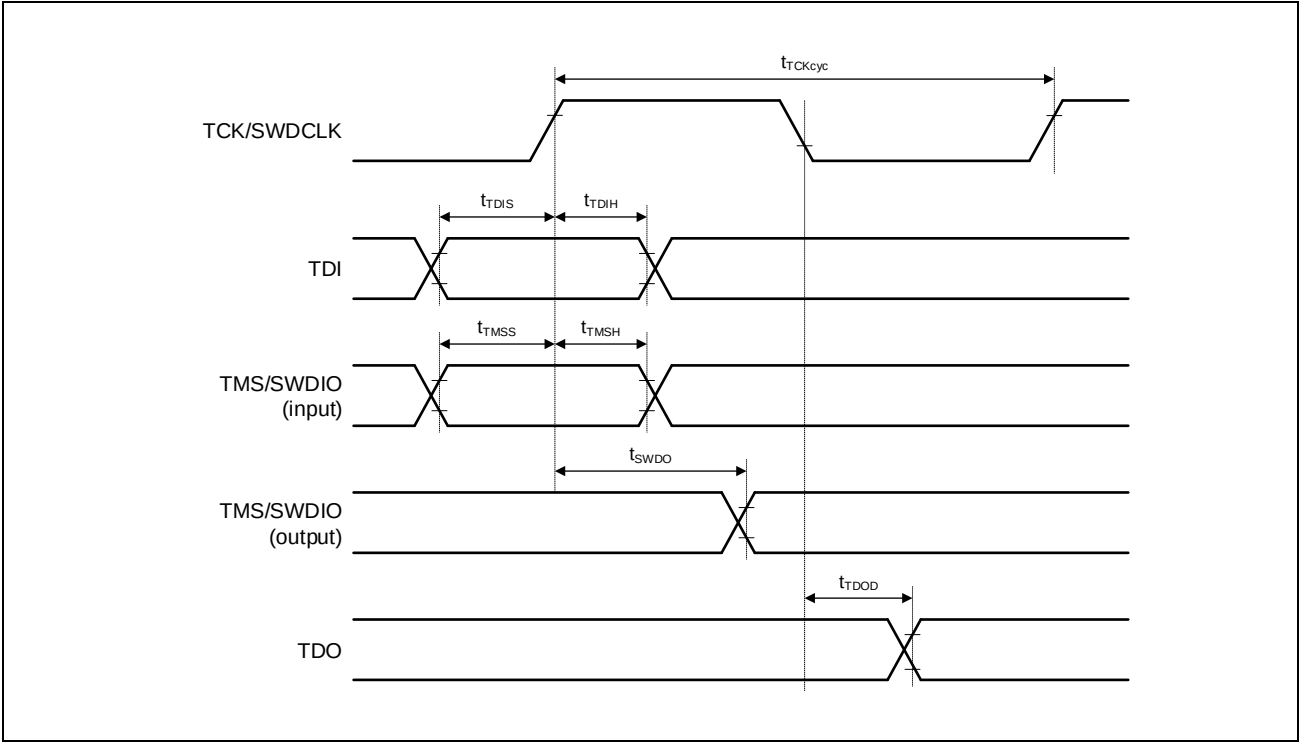


Figure 3.16 Data Transfer Timing

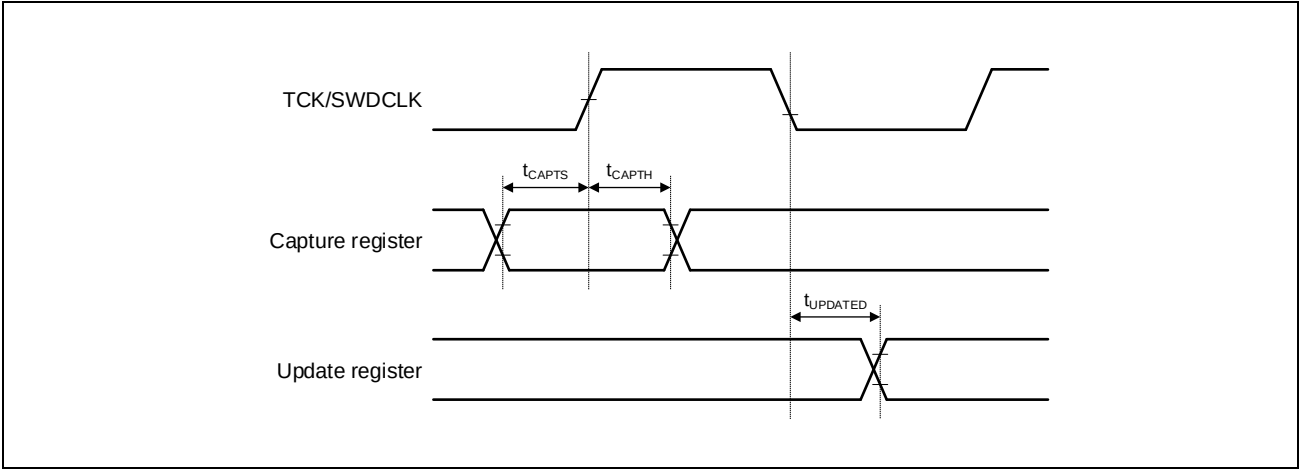


Figure 3.17 Boundary Scan Input/Output I/O Timing

3.5.6 SPI Multi I/O Bus Controller Access Timing

Table 3.22 SPI Multi I/O Bus Controller Access Timing

Item		Symbol	1.8 V		3.3 V		Unit	Figures
			(Serial flash/octal-SPI flash connected)		(Serial flash connected)			
			Min.	Max.	Min.	Max.		
Clock cycle		t _{SPBcyc}	15.0	—	15.0	—	ns	Figure 3.18
CLK high pulse width		t _{SPBWH}	0.45	0.55	0.45	0.55	t _{SPBcyc}	Figure 3.18
CLK low pulse width		t _{SPBWL}	0.45	0.55	0.45	0.55	t _{SPBcyc}	Figure 3.18
CLK rise time		t _{SPBR}	—	1.0	—	3.2	ns	Figure 3.18
CLK fall time		t _{SPBF}	—	1.0	—	3.2	ns	Figure 3.18
Data input setup time	QSPI0_SPCLK base point (SDR mode timing adjusted)	t _{SU}	6.7	—	7.5	—	ns	Figure 3.19
	QSPI0_SPCLK base point (DDR mode timing adjusted)		4.5	—	4.5	—	ns	Figure 3.20
Data input hold time	QSPI0_SPCLK base point (SDR mode timing adjusted)	t _H	0.5	—	0.5	—	ns	Figure 3.19
	QSPI0_SPCLK base point (DDR mode timing adjusted)		1.0	—	1.0	—	ns	Figure 3.20
SSL setup time		t _{LEAD}	1.5 × t _{SPBcyc} – 3	8.5 × t _{SPBcyc} + 3	1.5 × t _{SPBcyc} – 3	8.5 × t _{SPBcyc} + 3	ns	Figure 3.19, Figure 3.20
SSL hold time		t _{LAG}	1 × t _{SPBcyc} – 3	8 × t _{SPBcyc} + 3	1 × t _{SPBcyc} – 3	8 × t _{SPBcyc} + 3	ns	Figure 3.19, Figure 3.20
Continuous transfer delay time		t _{TD}	1 × t _{SPBcyc} – 3	8 × t _{SPBcyc} + 3	1 × t _{SPBcyc} – 3	8 × t _{SPBcyc} + 3	ns	Figure 3.19, Figure 3.20
Data output delay time	SDR	t _{OD}	—	2.0	—	5.0	ns	Figure 3.19
	DDR		—	6.5*2	—	7.5*3	ns	Figure 3.20
Data output hold time	SDR	t _{OH}	-2.0	—	-5.0	—	ns	Figure 3.19
	DDR		1.0*2	—	2.1*3	—	ns	Figure 3.20
Data output buffer off time	SDR	t _{BOFF}	—	2.0	—	3.0	ns	Figure 3.21
	DDR		—	2.0	—	3.0	ns	Figure 3.21

Note 1. Output load: 15 pF/driving ability: 12 mA

Note 2. QSPI0_SPCLK frequency: 100 MHz.

Note 3. QSPI0_SPCLK frequency: 66 MHz

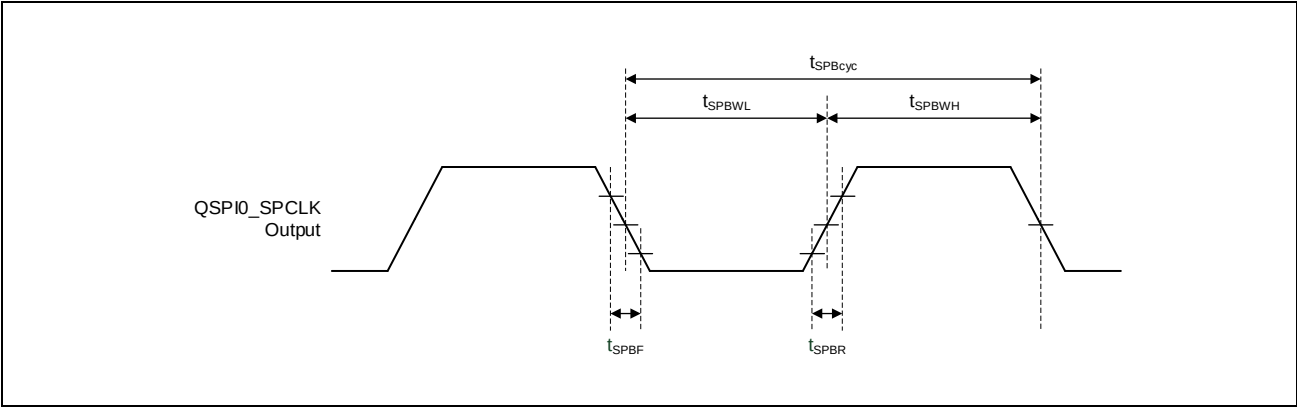


Figure 3.18 Clock Timing

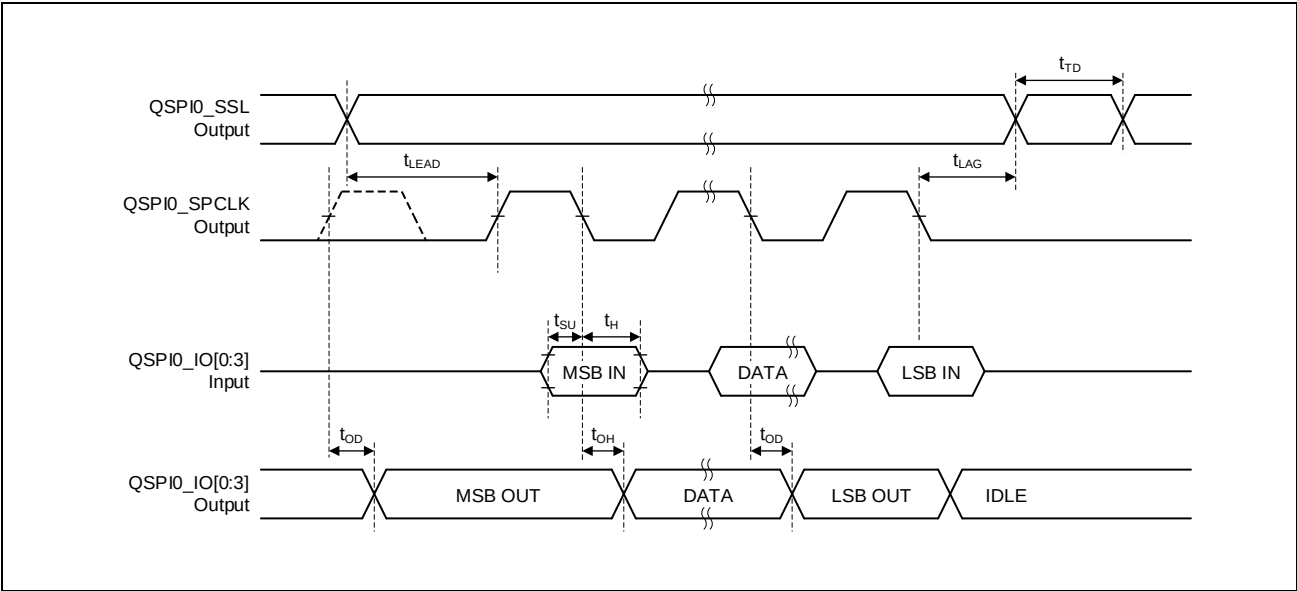


Figure 3.19 SDR Transfer Format Transmission and Reception Timing

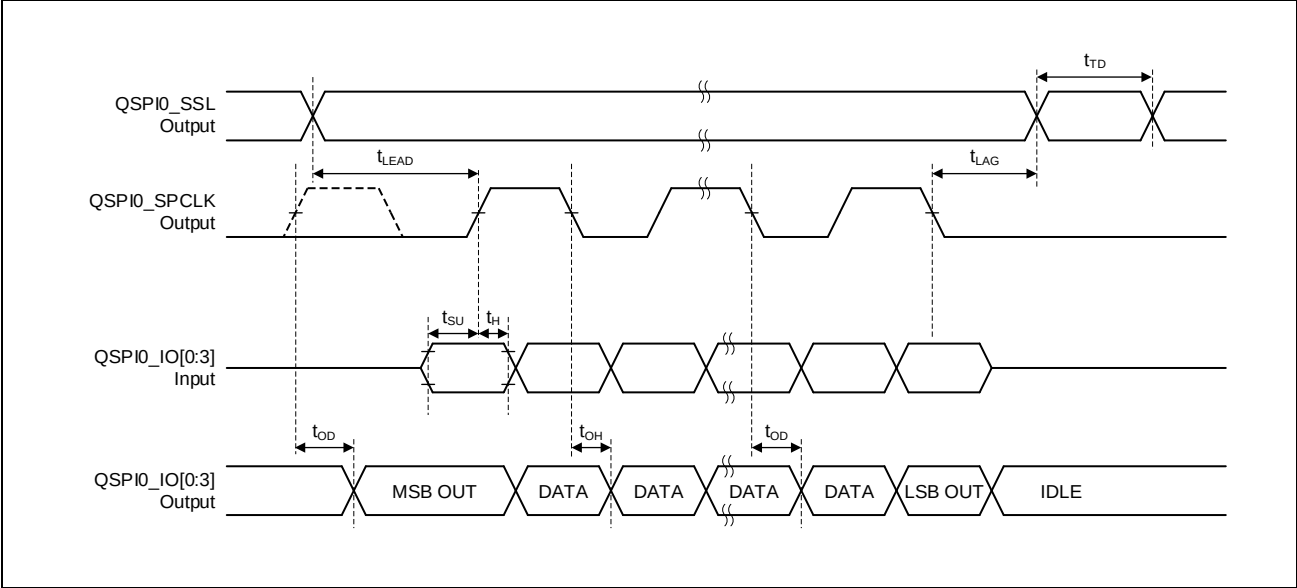


Figure 3.20 DDR Transfer Format Transmission and Reception Timing

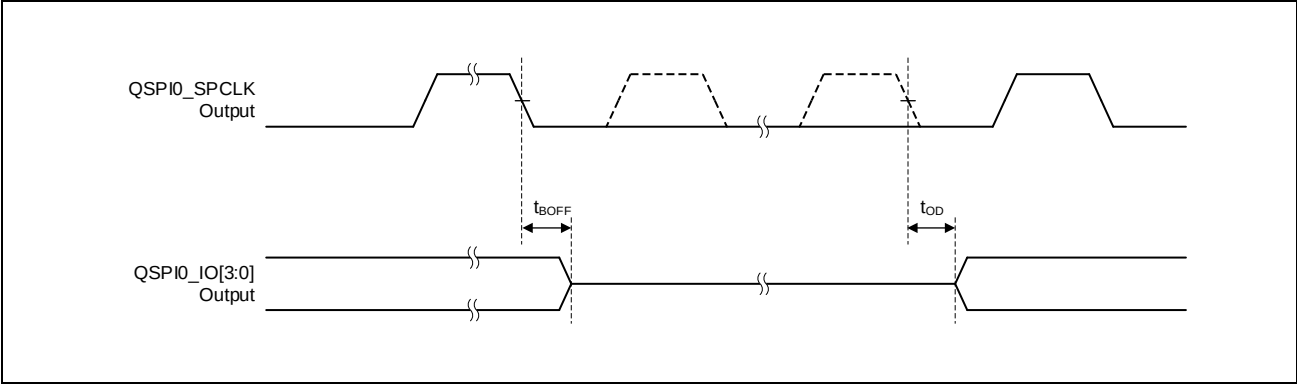


Figure 3.21 Timing for Switching the Buffers On and Off

3.5.7 Control Signal Access Timing

Table 3.23 Control Signal Timing

Item	Symbol	Min.	Max.	Unit	Figures
PRST# pulse width	t_{RESW}	20	—	t_{cyc}^{*1}	Figure 3.22
TRST# pulse width	t_{TRSW}	20	—	t_{cyc}^{*1}	
NMI pulse width	t_{NMIW}	20	—	t_{cyc}^{*1}	Figure 3.24
IRQ pulse width	t_{IRQW}	20	—	t_{cyc}^{*1}	
TINT pulse width	t_{TINTW}	20	—	t_{cyc}^{*1}	
PRST# input rise time	t_{RSr}	—	500	μs	Figure 3.23

Note 1. $t_{cyc} = 41.666 \text{ ns}$ (24 MHz)

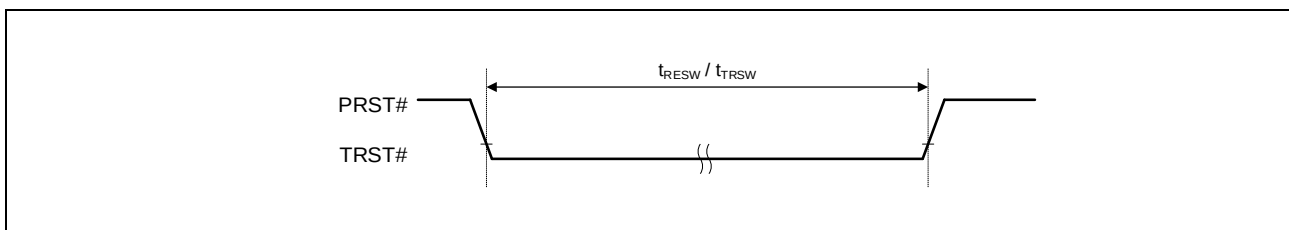


Figure 3.22 Reset Input Timing 1

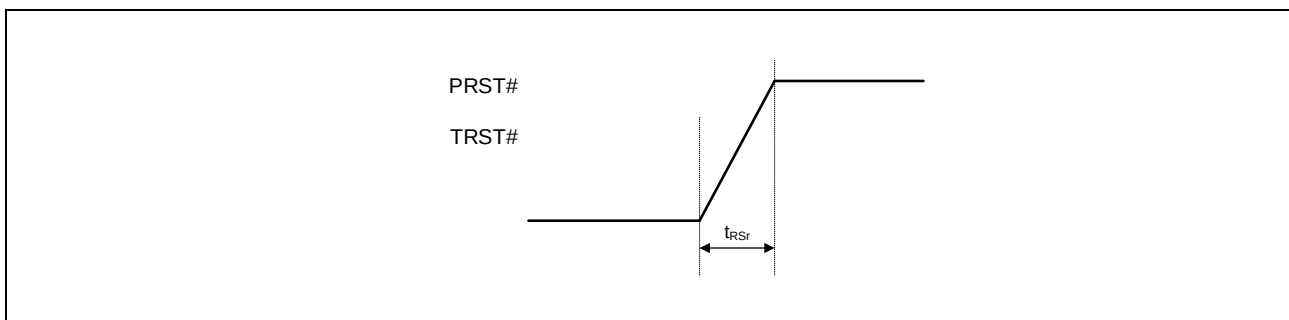


Figure 3.23 Reset Input Timing 2

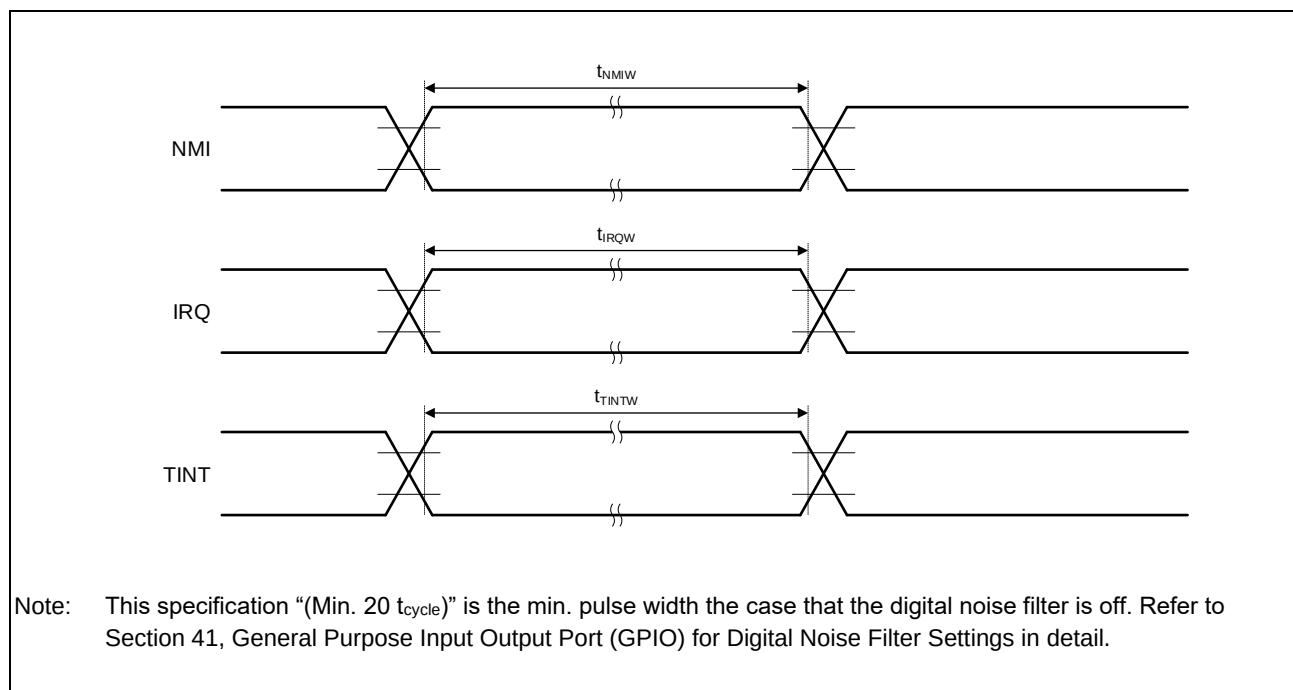


Figure 3.24 Interrupt Signal Input Timing

3.5.8 Serial Sound Interface (SSIF-2) Access Timing

Table 3.24 SSIF-2 Timing

Item	I/O	Symbol	Min.	Max.	Unit	Figures
Output clock cycle	Output	t_O	80	64000	ns	Figure 3.25
Input clock cycle	Input	t_i	80	—	ns	
Clock high	Bidirectional	t_{HC}	32	—	ns	
Clock low		t_{LC}	32	—	ns	
Clock rise time/clock fall time	Output	t_{RC}/t_{FC}	—	25	ns	
Setup time	Input	t_{SR}	25	—	ns	Figure 3.26,
Hold time		t_{HR}	5	—	ns	Figure 3.27,
SILRCK output delay time	Output	t_{DTR}	—5	25	ns	Figure 3.28
Data output delay time (Noise canceler not in use)		t_{DTR}	—5	25	ns	
Data output delay time (Noise canceler in use)		t_{DTR}	10	50	ns	

Note: AC access timing condition: drive ability 12mA, output load 30pF, slew rate = fast

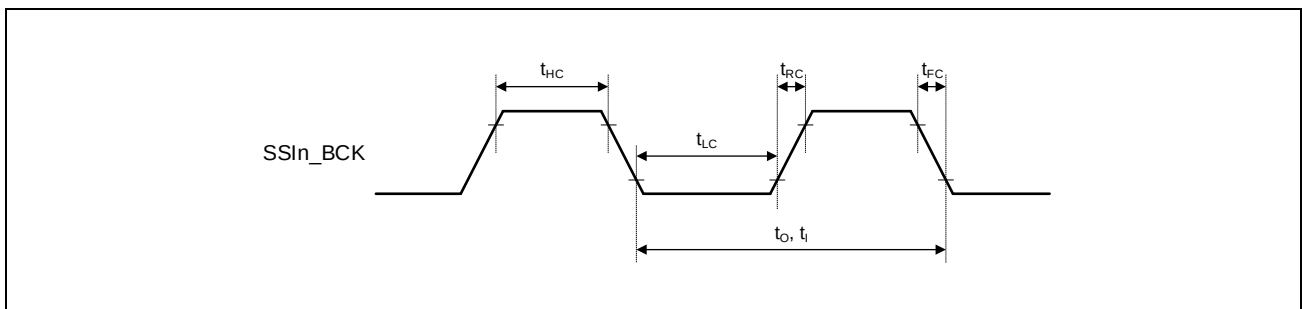


Figure 3.25 Bit Clock Input/Output Timing

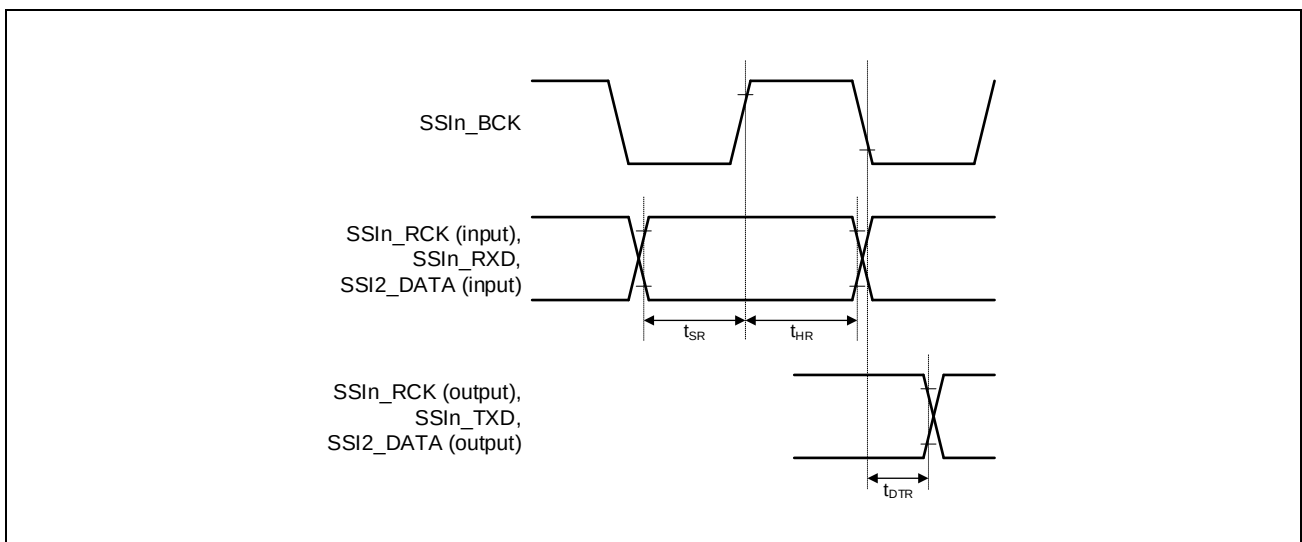


Figure 3.26 Transmission and Reception Timing (SSIBCK Falling Output)

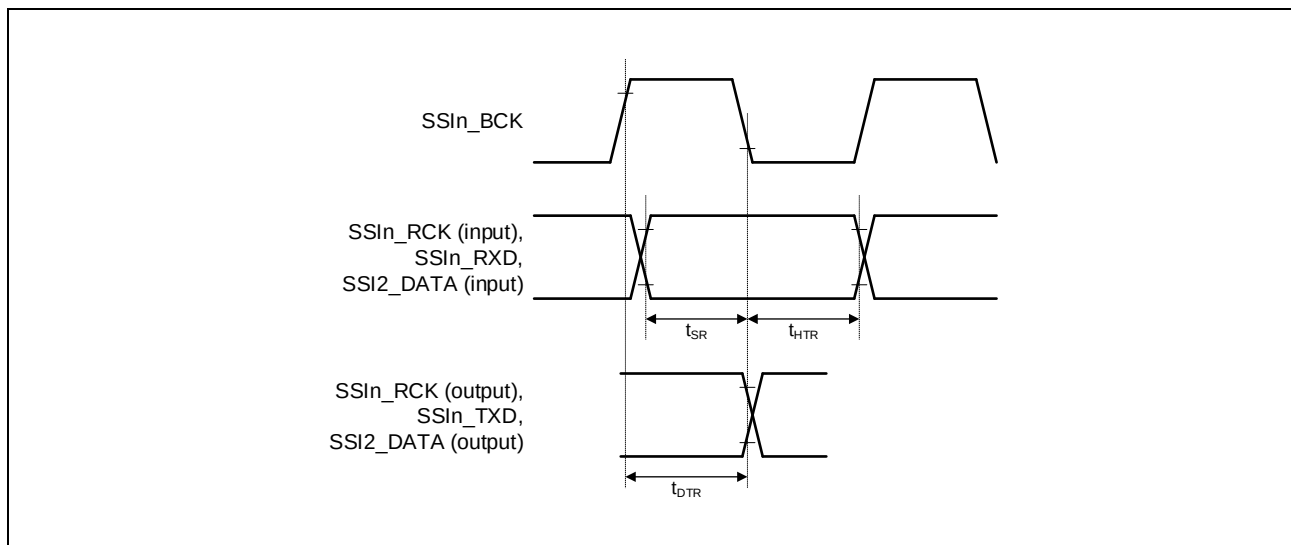


Figure 3.27 Transmission and Reception Timing (SSIBCK Rising Output)

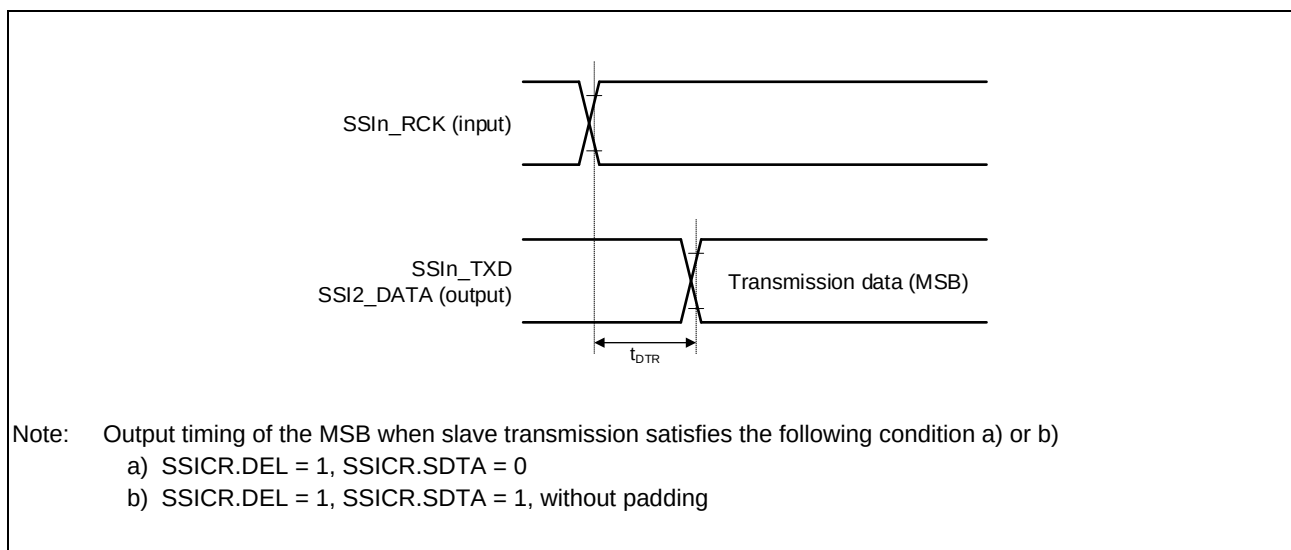


Figure 3.28 Transmission Timing (Slave, in Synchronization with SSILRCK)

3.5.9 Multi-Function Timer Pulse Unit 3 (MTU3a) Access Timing

Table 3.25 MTU3a Timing

Item			Symbol	Min.	Max.	Unit*1	Figures
MTU3a	Input capture input pulse width	Single-edge setting	t_{MTICW}	1.5	—	t_{p1cyc}^{*1}	Figure 3.29
		Both-edge setting		2.5	—		
	Timer clock pulse width	Single-edge setting	t_{MTCKWH}	1.5	—	t_{p1cyc}^{*1}	Figure 3.30
		Both-edge setting	t_{MTCKWL}	2.5	—		
		Phase counting mode		2.5	—		

Note: AC access timing condition: drive ability 4mA, output load 30pF, slew rate = fast

Note 1. t_{p1cyc} indicates peripheral clock means MTU_X_MCLK_MTU3 (P0φ).

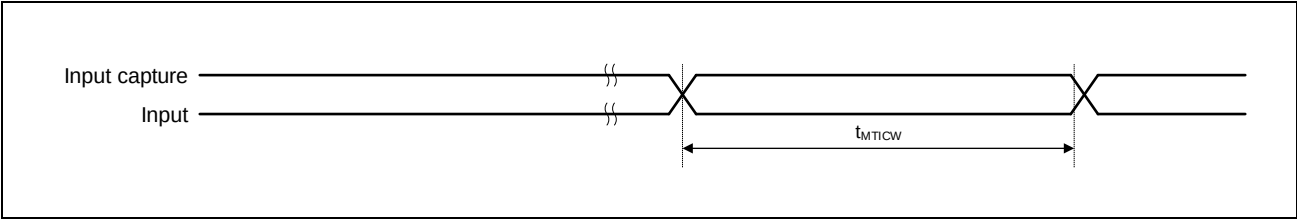


Figure 3.29 MTU3a Input Capture Input Timing

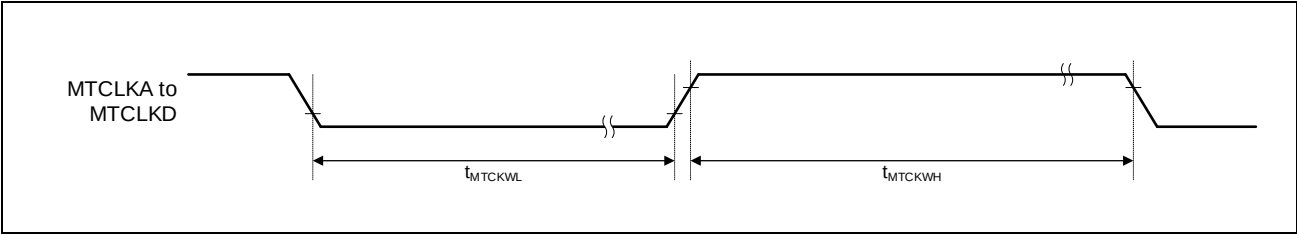


Figure 3.30 MTU3a Clock Input Timing

3.5.10 Port Output Enable 3 (POE3) Access Timing

Table 3.26 POE3 Timing

Item		Symbol	Min.	Max.	Unit	Figures
POE3	POEn# input pulse width	t_{POE3W}	1.5	—	t_{p1cy}^{*1}	Figure 3.31

Note 1. t_{p1cy} indicates peripheral clock means POE3_CLKM_POE (P0 ϕ).

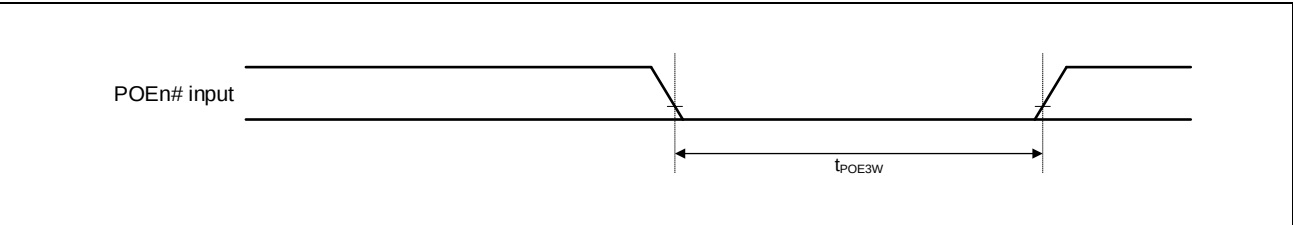


Figure 3.31 POEn# Input Pulse Timing

3.5.11 I²C Bus Interface Access Timing

Table 3.27 I²C Bus Interface Timing

Item	Symbol	I/O	Standard Mode (Sm)		Fast Mode (Fm)		Fast Mode Plus (Fm+)		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	
SCL clock frequency	f _{CLK}	I/O	0	100	0	400	0	1000	kHz
Bus free time (between stop and start condition)	t _{BUF}	I/O	4.7	—	1.3	—	0.5	—	μs
Hold time* ¹	t _{HD:STA}	I/O	4.0	—	0.6	—	0.26	—	μs
Low period of SCL clock	t _{LOW}	I/O	4.7	—	1.3	—	0.5	—	μs
High period of SCL clock	t _{HIGH}	I/O	4.0	—	0.6	—	0.26	—	μs
Setup time for start / restart condition	t _{SU:STA}	I/O	4.7	—	0.6	—	0.26	—	μs
Data hold time (I ² C bus device)	t _{HD:DAT}	I/O	0* ²	—	0* ²	—	0	—	μs
Data setup time	t _{SU:DAT}	I/O	250	—	100* ³	—	50	—	ns
SDA and SCL signal rise time	t _R	Input	—	1000	20	300	—	120	ns
SDA and SCL signal fall time* ³	t _F	Input	—	300	20 × (P _{VDD} /5.5 V)	300	20 × (P _{VDD} /5.5 V)	120	ns
		Output	—	300	20 × (P _{VDD} /5.5 V)* ⁶	300* ⁶	20 × (P _{VDD} /5.5 V)* ⁷	120* ⁷	ns
Setup time for STOP condition	t _{SU:STO}	I/O	4.0	—	0.6	—	0.26	—	μs
Capacitive load for each bus line	C _b	—	—	400* ⁴	—	400* ⁴	—	550* ⁴	pF
Pulse width of spikes that must be suppressed by the input filter	t _{SP}	Input	—	—	0	50* ⁵	0	50* ⁵	ns

Note: In the above table and subsequently, SCL and SDA refer to the RIICnSCL and RIICnSDA signals, respectively.

Note: AC access timing condition: drive ability 4mA, output load 400pF, slew rate = slow

Note 1. The first clock pulse is generated on the SCL line after the start condition has been issued and the hold time has elapsed.

Note 2. This module requires a minimum of 300 ns hold time internally for the SDA signal to handle the period over which the falling edge of SCL has not reached a defined level (time until the CnSCL signal reaches V_{IL} (max.) from V_{IH} (min.)).

Note 3. The fast-mode I²C bus device can be used in the standard mode I²C bus system. In this case, the minimum value of the data setup time (t_{SU:DAT} (min.) 250 [ns]) must be satisfied.

If the system does not extend the low period of SCL clock (t_{LOW}), this condition is automatically satisfied. If the system extends the low period of SCL clock (t_{LOW}), transmit the subsequent data bit to the SDA line before the SCL line is released (t_R (max.) + t_{SU:DAT} (min.) = 1000 + 250 = 1250 [ns]: (standard mode I²C bus specification)).

Note 4. Total capacitance of one bus line. The allowable maximum bus capacitance may differ from this specification, depending on the actual operating voltage and frequency of an application. For techniques to cope with a large bus capacitance, see the I²C bus specification provided by NXP Semiconductors.

Note 5. Noise is removed by the analog and digital input filters. The level of noise reduction of the digital input filter is determined by the period of internal reference clock (IICφ) and the NF[1:0] bits in RIICnMR3. For details, refer to Section 26, I²C Bus Interface.

Note 6. External pull-up resistor is required 1077Ω to 1770Ω when using RIIC ch2 or RIIC ch3.

Note 7. External pull-up resistor is required 240Ω to 257Ω when using RIIC ch2 or RIIC ch3.

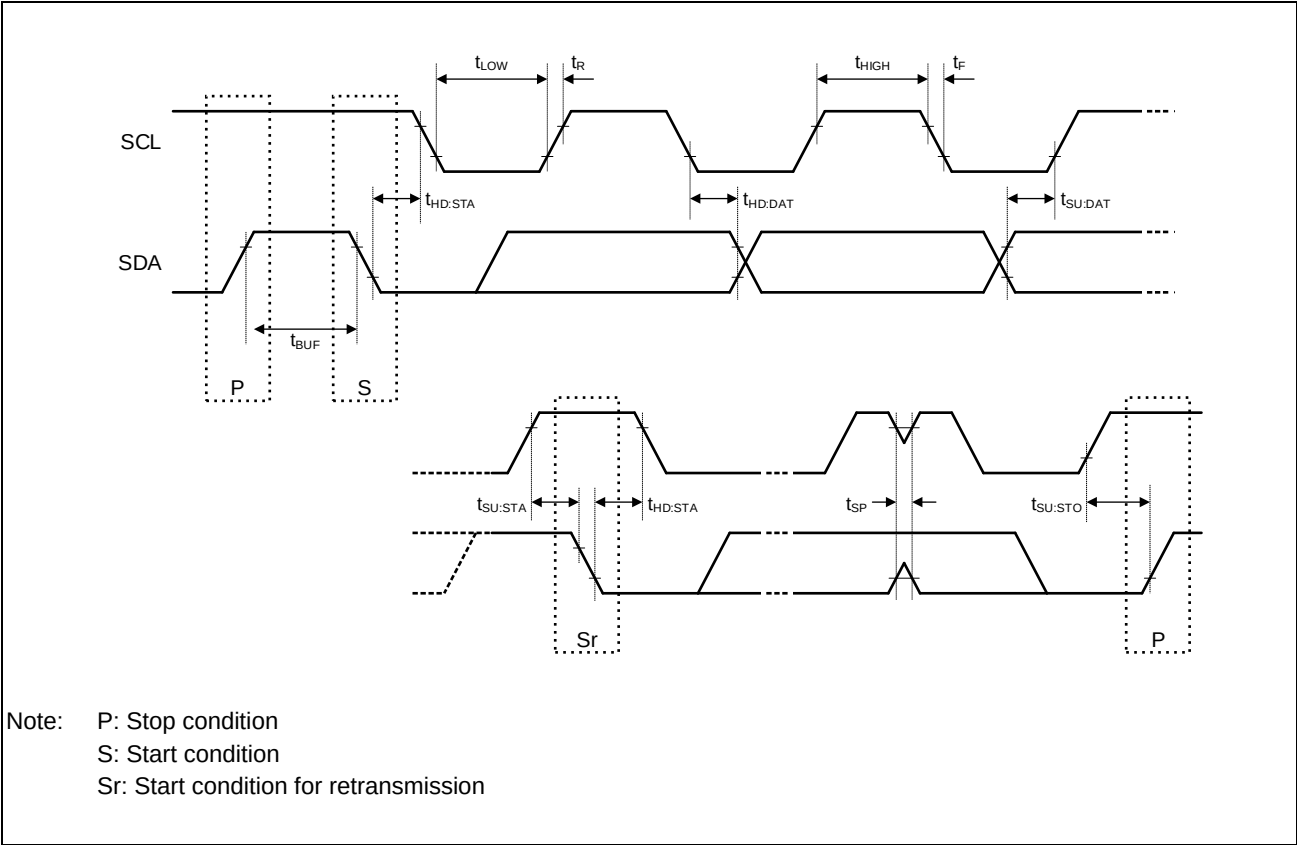


Figure 3.32 Input/Output Timing

3.5.12 Serial Communications Interface with FIFO (SCIFA) Access Timing

Table 3.28 SCIFA Timing

Item			Symbol	Min.	Max.	Unit	Figures
SCIFA	Input clock cycle	Asynchronous	t_{Scyc}	4	—	t_{p1cyc}^{*1}	Figure 3.33
		Clocked synchronous		12	—		
	Input clock pulse width		t_{SCKW}	0.4	0.6	t_{p1cyc}^{*1}	
	Input clock rise time		t_{SCKr}	—	5	ns	
	Input clock fall time		t_{SCKf}	—	5	ns	
	Output clock cycle	Asynchronous*2	t_{Scyc}	8	—	t_{p1cyc}^{*1}	
		Clocked synchronous		4	—		
	Output clock pulse width		t_{SCKW}	0.4	0.6	t_{p1cyc}^{*1}	
	Output clock rise time		t_{SCKr}	—	9	ns	
	Output clock fall time		t_{SCKf}	—	9	ns	
	Transmit data delay time	Internal clock	t_{TXD}	−10	10	ns	Figure 3.34
		External clock		$3 \times t_{p1cyc}^{*1}$	$4 \times t_{p1cyc}^{*1} + 20$		
	Receive data setup time	Internal clock	t_{RXS}	$3 \times t_{p1cyc}^{*1} + 20$	—	ns	
		External clock		$t_{p1cyc}^{*1} + 10$	—		
	Receive data hold time	Internal clock	t_{RXH}	$-3 \times t_{p1cyc}^{*1}$	—	ns	
		External clock		$2 \times t_{p1cyc}^{*1} + 10$	—		

Note: AC access timing condition: drive ability 12mA, output load 30pF, slew rate = fast

Note 1. t_{p1cyc} indicates peripheral clock means SCIFn_CLK_PCK (P0φ) (n = 0 to 4).

Note 2. When the SEMR.ABCS0 and SEMR.BGDM bits are set to 1.

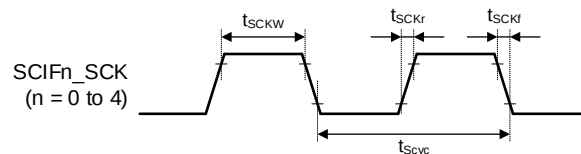


Figure 3.33 SCK Input Clock Timing

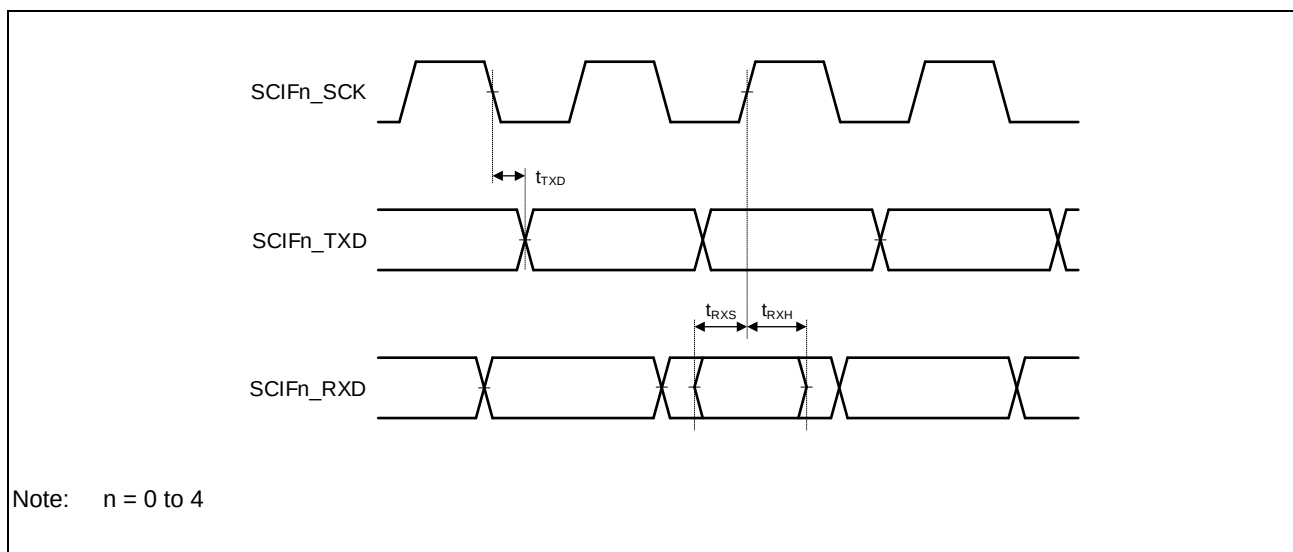


Figure 3.34 SCIFA Input/Output Timing in Clocked Synchronous Mode

3.5.13 Serial Communications Interface (SCIg) Access Timing

Table 3.29 SCIg Timing

Item			Symbol	Min.	Max.	Unit	Figures
SCIg	Input clock cycle	Asynchronous	t_{Scyc}	4	—	t_{p1cyc}^{*1}	Figure 3.35
		Clocked synchronous		6	—		
	Input clock pulse width		t_{SCKW}	0.4	0.6	t_{p1cyc}^{*1}	
	Input clock rise time		t_{SCKr}	—	5	ns	
	Input clock fall time		t_{SCKf}	—	5	ns	
	Output clock cycle	Asynchronous*2	t_{Scyc}	8	—	t_{p1cyc}^{*1}	
		Clocked synchronous		4	—		
	Output clock pulse width		t_{SCKW}	0.4	0.6	t_{p1cyc}^{*1}	
	Output clock rise time		t_{SCKr}	—	5	ns	
	Output clock fall time		t_{SCKf}	—	5	ns	
	Transmit data delay time	Clocked synchronous	t_{TXD}	—	28	ns	Figure 3.36
	Receive data setup time	Clocked synchronous	t_{RXS}	15	—	ns	
	Receive data hold time	Clocked synchronous	t_{RXH}	5	—	ns	

Note: AC access timing condition: drive ability 12mA, output load 30pF, slew rate = fast

Note 1. t_{p1cyc} indicates peripheral clock means SCIn_SCK (P0φ) (n = 0 to 1).

Note 2. When the SEMR.ABCS0 and SEMR.BGDM bits are set to 1.

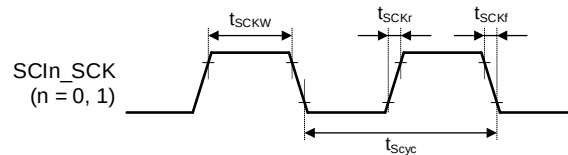


Figure 3.35 SCK Input Clock Timing

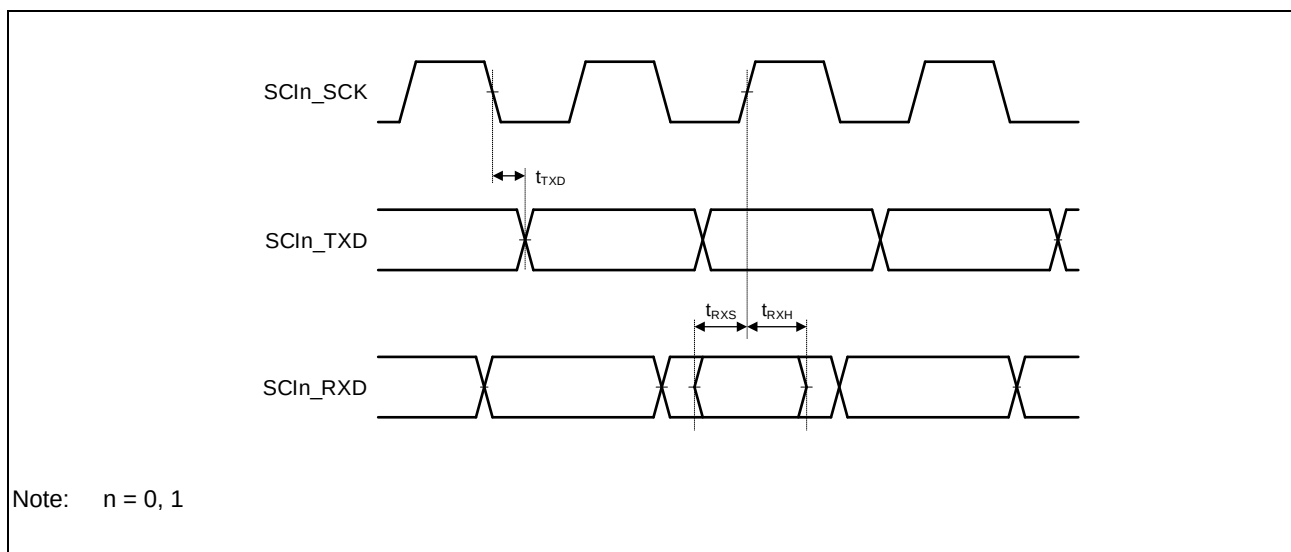


Figure 3.36 SCIFA Input/Output Timing in Clocked Synchronous Mode

3.5.14 Renesas Serial Peripheral Interface (RSPI) Access Timing

Table 3.30 Renesas Serial Peripheral Interface Timing

Item		Symbol	Min.	Max.	Unit	Figure
RSPCK clock cycle	Master	t_{SPCyc}	2	4096	t_{p1cyc}^{*1}	Figure 3.37
	Slave		8	4096		
RSPCK clock high pulse width	Master	t_{SPCKWH}	0.4	—	t_{SPCyc}^{*1}	
	Slave		0.4	—		
RSPCK clock low pulse width	Master	t_{SPCKWL}	0.4	—	t_{SPCyc}^{*1}	
	Slave		0.4	—		
Data input setup time	Master	t_{SU}	9	—	ns	Figure 3.38 to Figure 3.41
	Slave		0	—	t_{p1cyc}^{*1}	
Data input hold time	Master	t_H	0	—	ns	
	Slave		4	—	t_{p1cyc}^{*1}	
SSL setup time	Master	t_{LEAD}	$1 \times t_{SPCyc} - 20$	$8 \times t_{SPCyc}$	ns	
	Slave		4	—	t_{p1cyc}^{*1}	
SSL hold time	Master	t_{LAG}	$1 \times t_{SPCyc}$	$8 \times t_{SPCyc} + 20$	ns	
	Slave		4	—	t_{p1cyc}^{*1}	
Data output delay time	Master	t_{OD}	—	16	ns	
	Slave		—	4	t_{p1cyc}^{*1}	
Data output hold time	Master	t_{OH}	0	—	ns	
	Slave		2	—	t_{p1cyc}^{*1}	
Continuous transmission delay time	Master	t_{TD}	$1 \times t_{SPCyc} + 2 \times t_{cyc}$	$8 \times t_{SPCyc} + 2 \times t_{cyc}$	ns	
	Slave		$4 \times t_{cyc}$	—		
Slave access time		t_{SA}	—	4	t_{p1cyc}^{*1}	Figure 3.40, Figure 3.41
Slave out release time		t_{REL}	—	3	t_{p1cyc}^{*1}	

Note: AC access timing condition: drive ability 12mA, output load 30pF, slew rate = fast

Note 1. t_{p1cyc} indicates peripheral clock means RSPIn_CLKB (P0φ) (0 to 2).

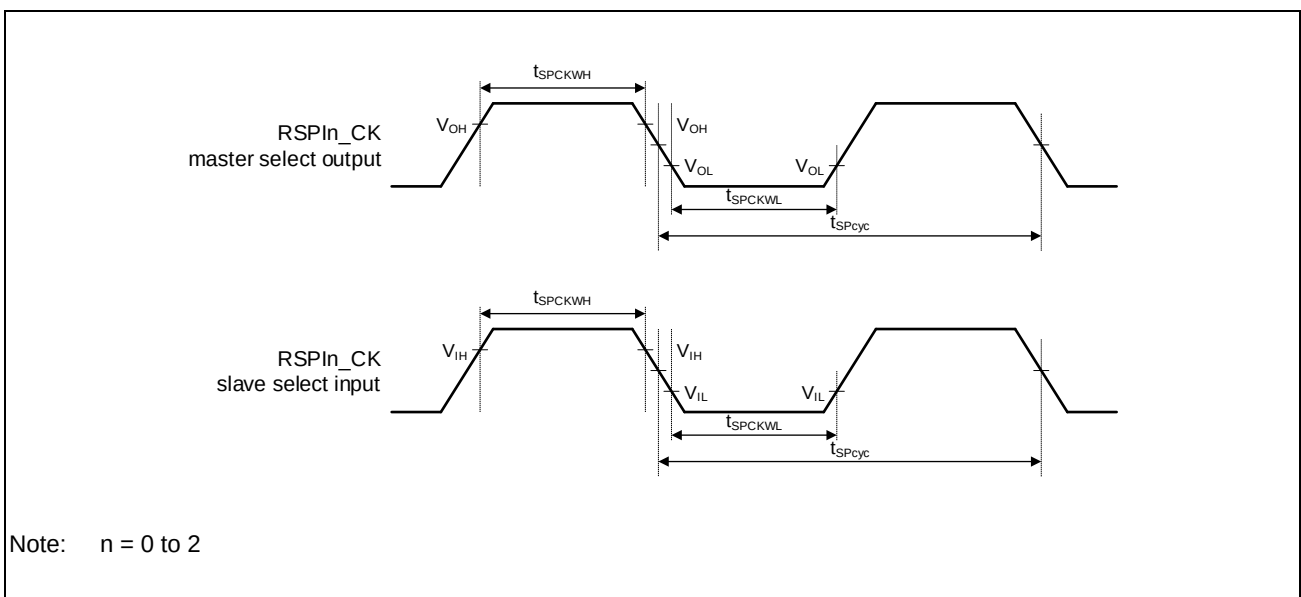


Figure 3.37 Clock Timing

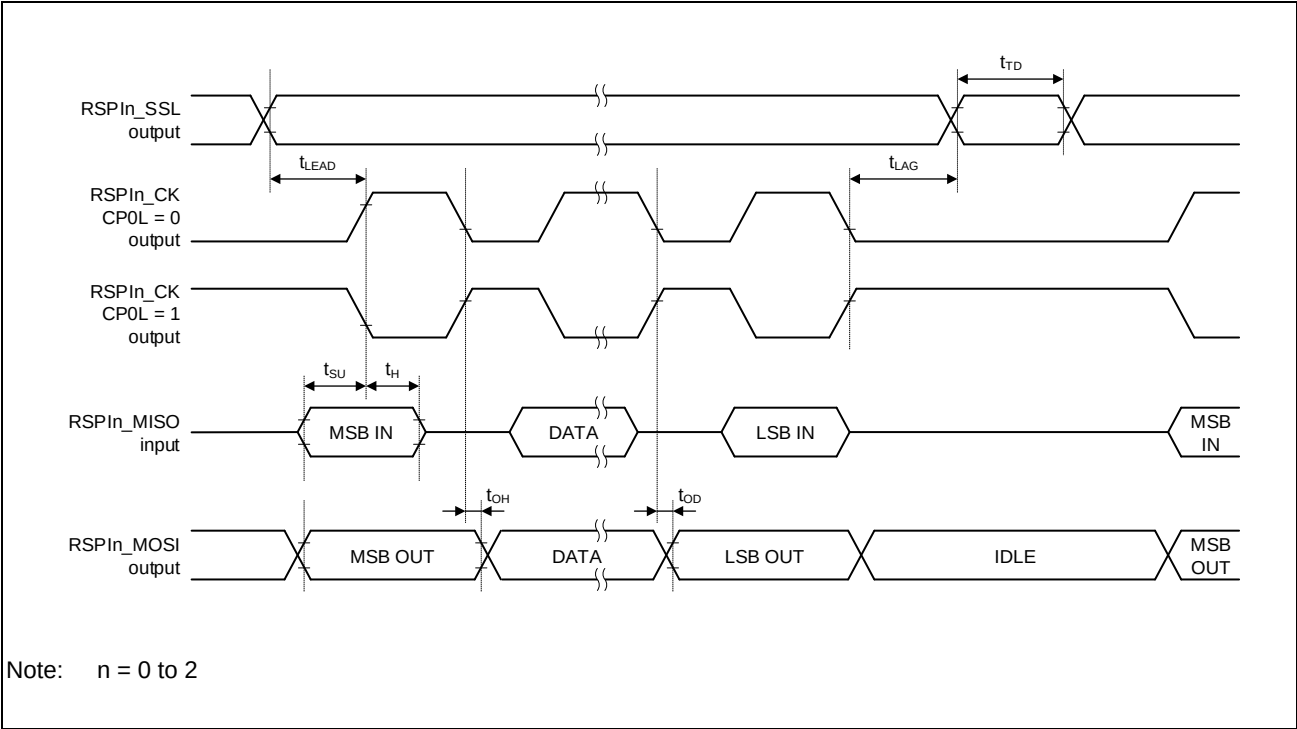


Figure 3.38 Transmission and Reception Timing (Master, CPHA = 0)

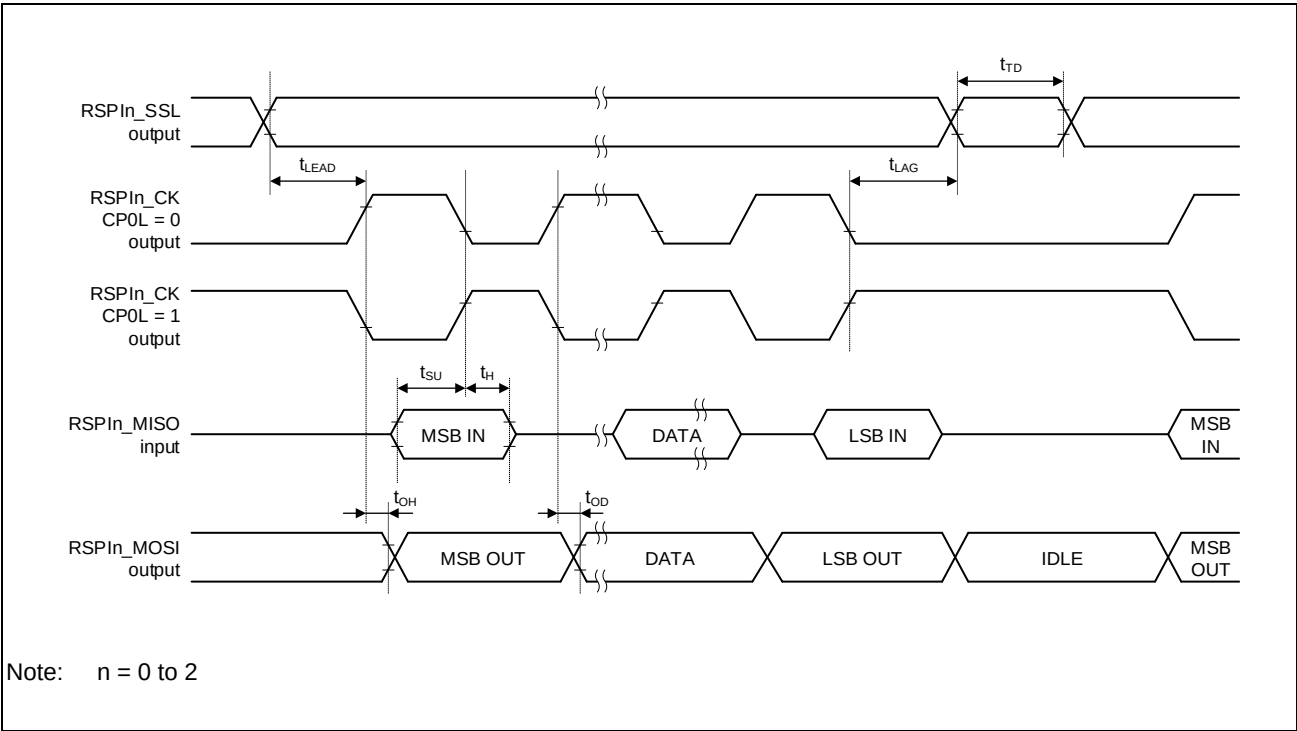


Figure 3.39 Transmission and Reception Timing (Master, CPHA = 1)

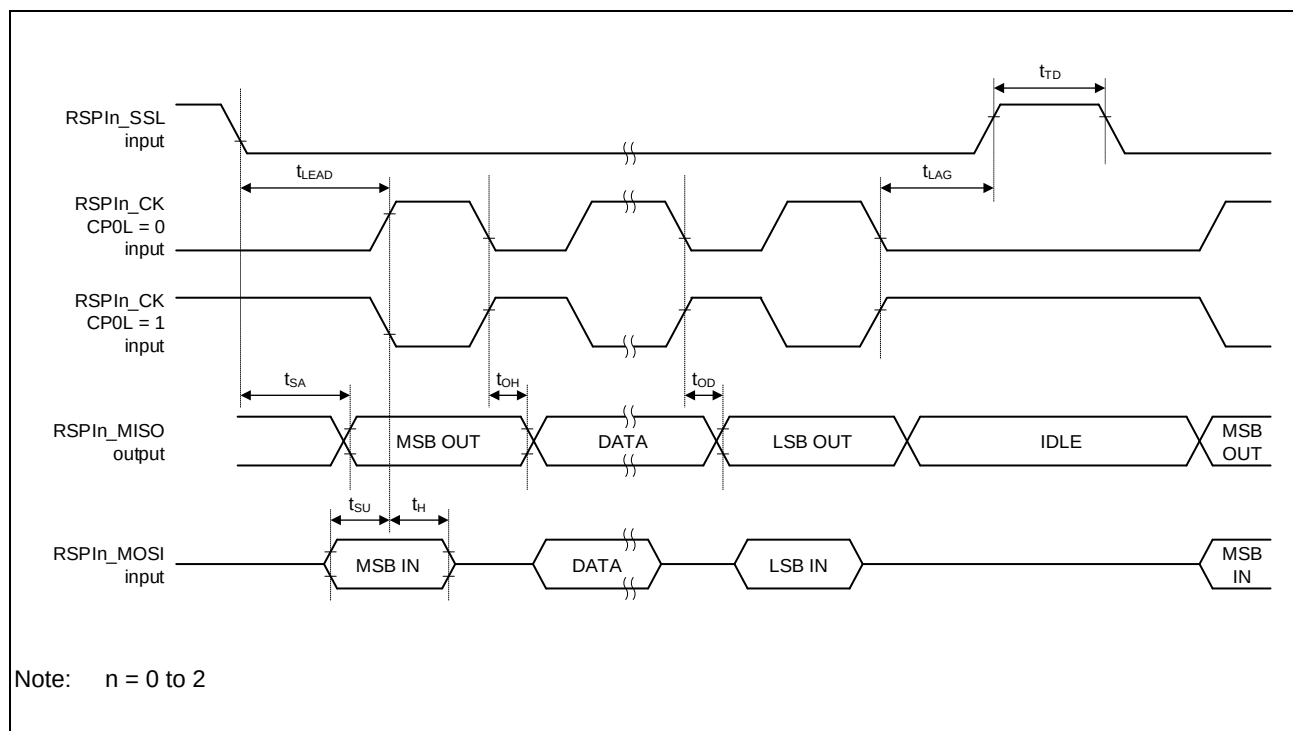


Figure 3.40 Transmission and Reception Timing (Slave, CPHA = 0)

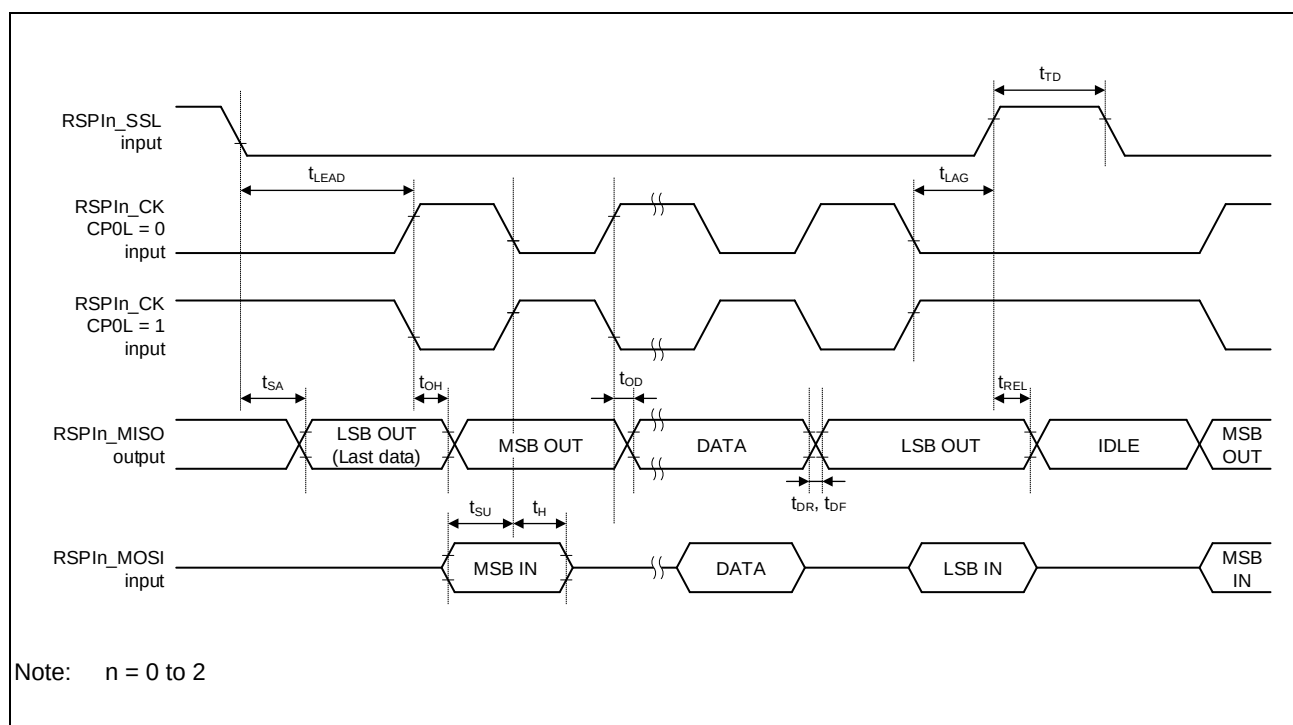


Figure 3.41 Transmission and Reception Timing (Slave, CPHA = 1)

3.5.15 Watchdog Timer Access Timing

Table 3.31 Watchdog Timer Timing

Item	Symbol	Min.	Max.	Unit	Figures
WDTOVF_PERROUT# Output Time	t_L	64	64	t_{P1cyc}^{*1}	Figure 3.42

Note 1. t_{P1cyc} indicates peripheral clock means WDTn_CLK (OSCCLK) (n = 0).

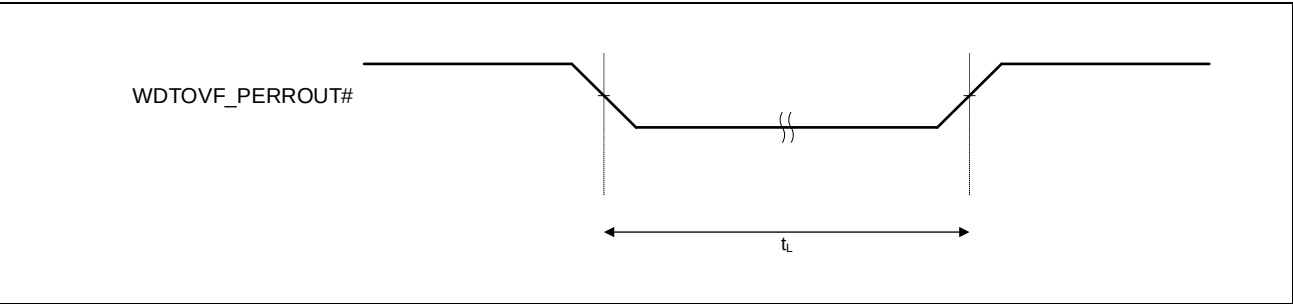


Figure 3.42 Watchdog Timer Output Timing

Section 4 Package Dimensions

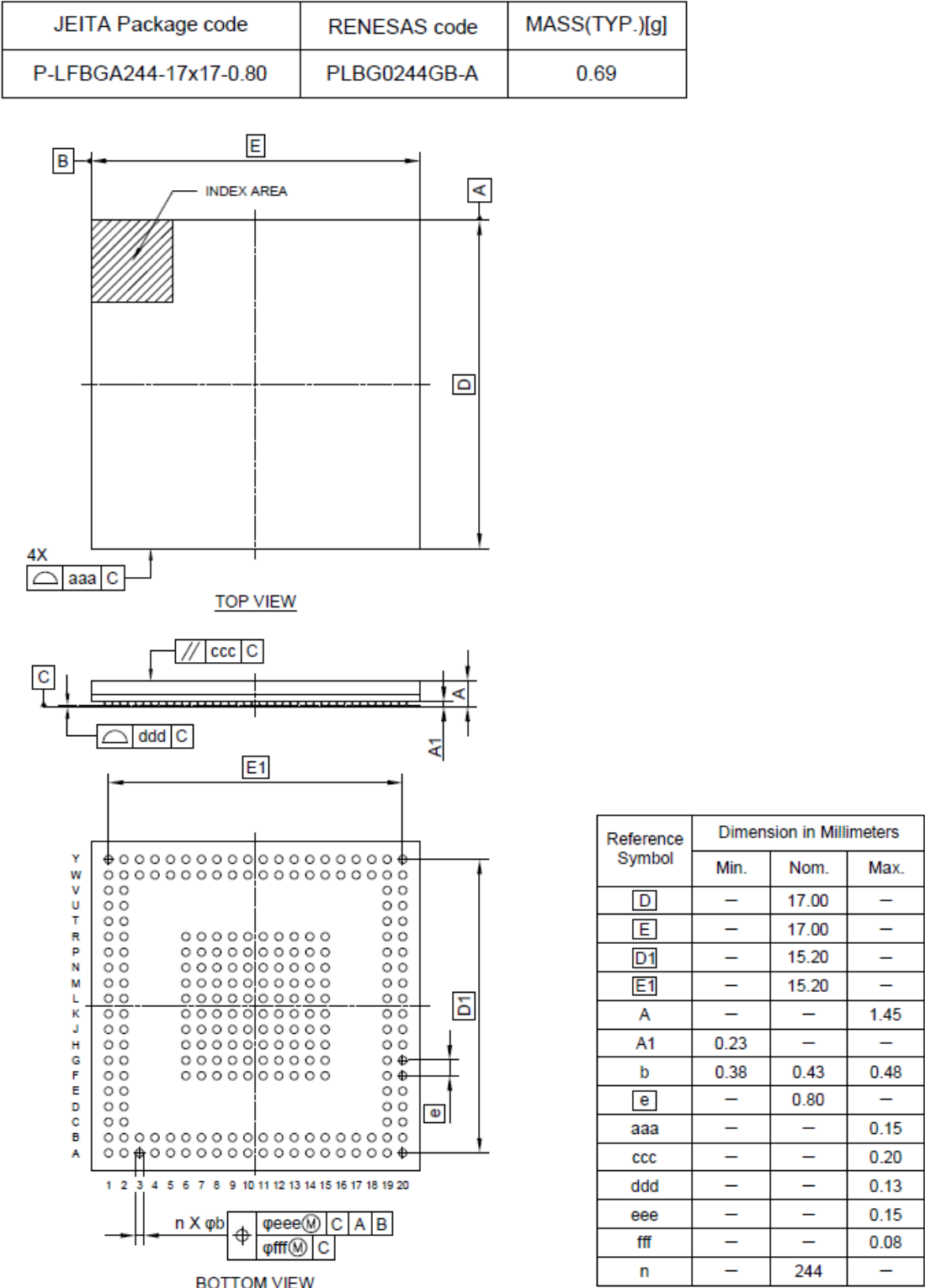


Figure 4-1 Package Dimensions

REVISION HISTORY	RZ/A3M Group Datasheet
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Rev.	Data	Description	
		Page	Summary
1.00	Dec 25, 2024	—	First edition issued
1.10	Mar 31, 2025	5	1.1.7 Sound Interface, SRC removed not to supported.
		8	1.2.15 Package description corrected, from BGA to LFBGA..
		9	1.2 Block Diagram, bus name changed from "MPU bus" to "MCPU bus".
		11	Section 2. description added same as for the hardware manual. 2.1 section title changed, and descriptions, corrected. 2.2 section title changed, and descriptions, corrected.
		18	3.4 DC Characteristics, Table 3.8 DC Characteristics (6) [1.8 V I/O (SD, QSPI)], VOH min's multiplied value corrected from 0.7 to 0.8, and VOL max's multiplied value corrected from 0.3 to 0.2.
		23	3.5.2.1 SDHI Access Timing (SDR 3.3-V), Table 3.16 SDHC AC Access Timing (SDR at 3.3-V Operation), Minimum condition value of Items (tSDWH, tSDWL, tSDODLY) are corrected.
		30	3.5.6 SPI Multi I/O Bus Controller Access Timing, Table 3.22 SPI Multi I/O Bus Contoller Access Timing, Minimum condition of 1.8V value of Item, "Clock cycle" is corrected.
		49	Figure A-1 number changed to Figure 4-1, Figure Title changed to remove "for LBGA 17□/0.8 mm pitch/244 pin".

General Precautions in the Handling of Microprocessing Unit and Microcontroller Unit Products

The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

5. Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

6. Voltage application waveform at input pin

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).

7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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